

Compact Quantum Dot based CW and ultrafast lasers for Biophotonics application

E. U. Rafailov

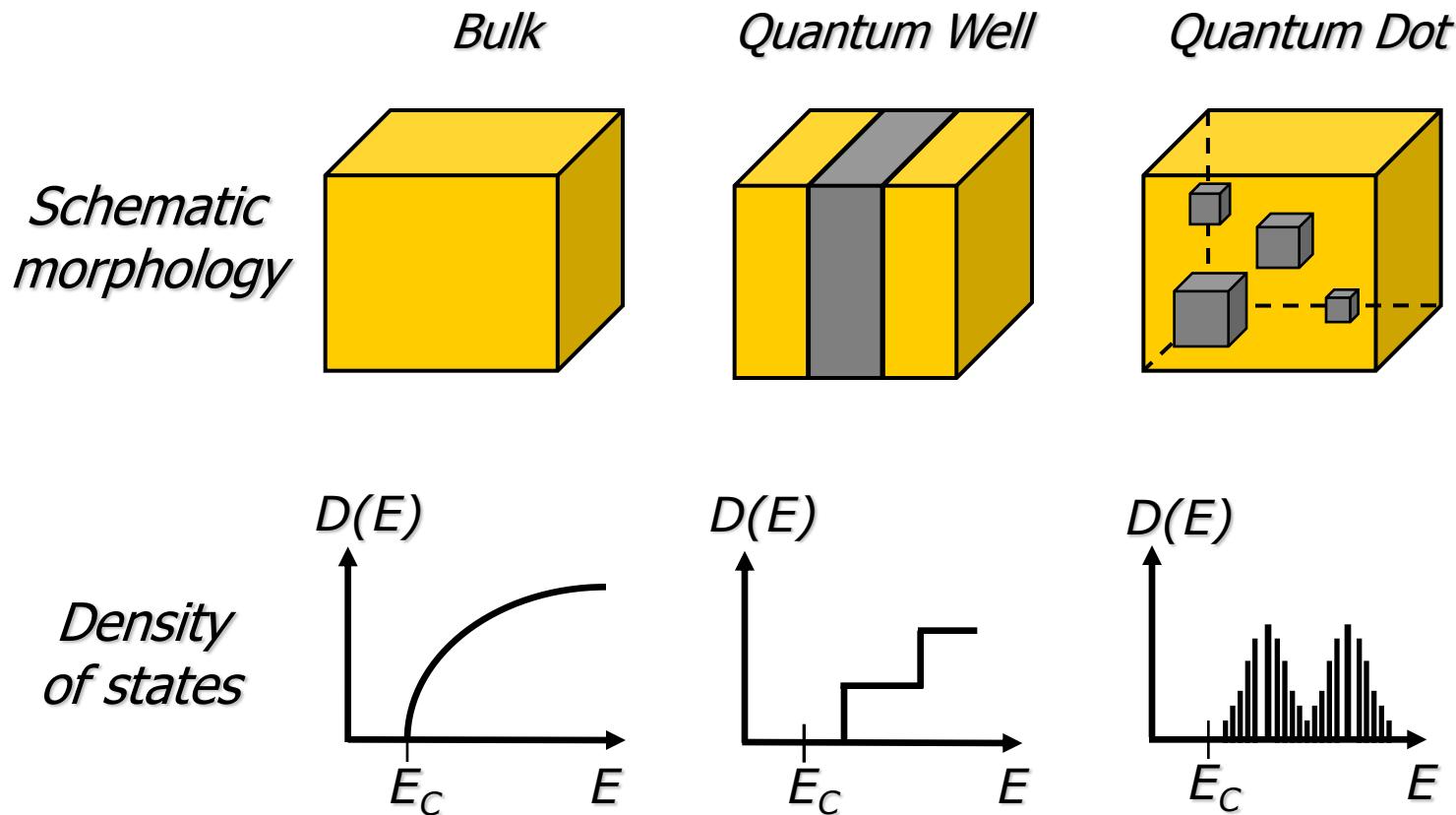
**Optoelectronics and Biomedical Photonics Group
School of Engineering and Applied Science**

**Aston University
Aston Triangle
Birmingham
UK**

Outline

- Quantum Dot materials
- InAs/GaAs Quantum Dot edge-emitting lasers
 - Continuous wave regime
 - Mode-locked regime
- Second-harmonic generation of QD edge-emitting lasers
- VECSELs
- Second-harmonic generation of VECSELs
- Biophotonics applications
- Conclusions

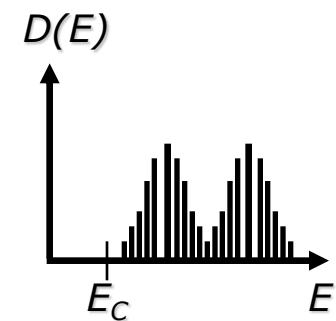
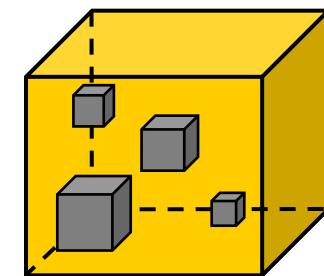
Quantum-dots structures



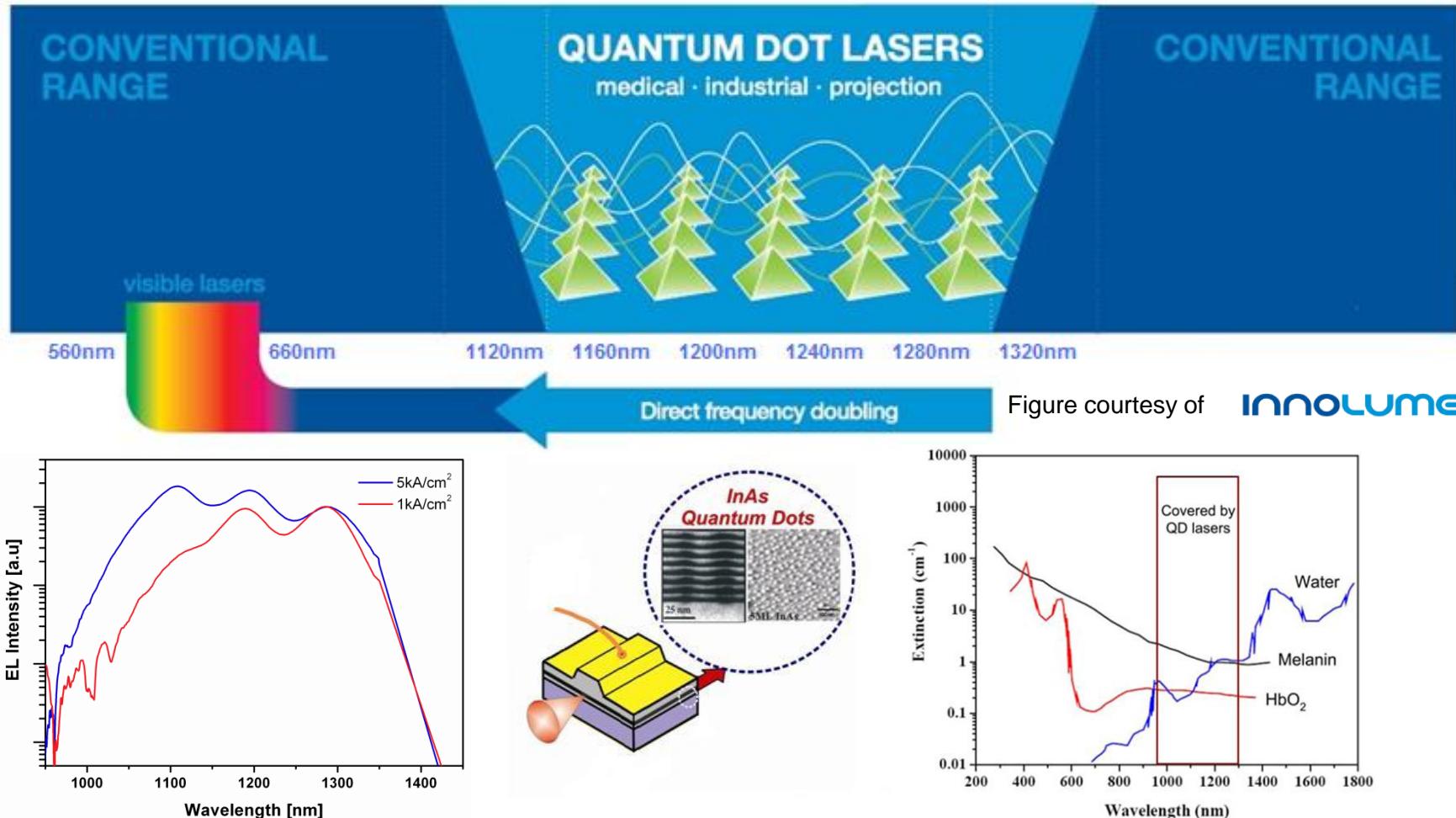
Quantum-dots for ultrafast devices

- Broad gain bandwidth
- Ultrafast carrier dynamics
- Low threshold current
- Low temperature sensitivity
- Lower absorption saturation fluence
- QD-SESAMs
- Great potential in THz radiation

Quantum Dot



InAs/GaAs Quantum Dot lasers



Ultra-broad electroluminescence spectra of a specially designed QD device

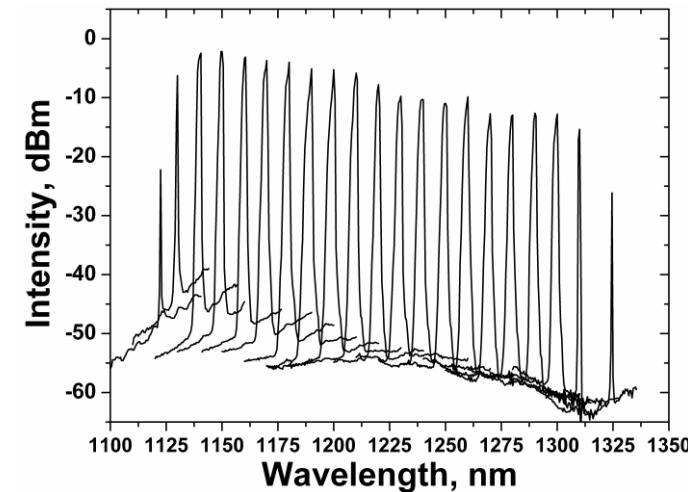
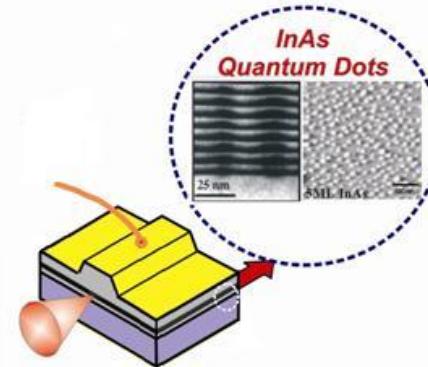
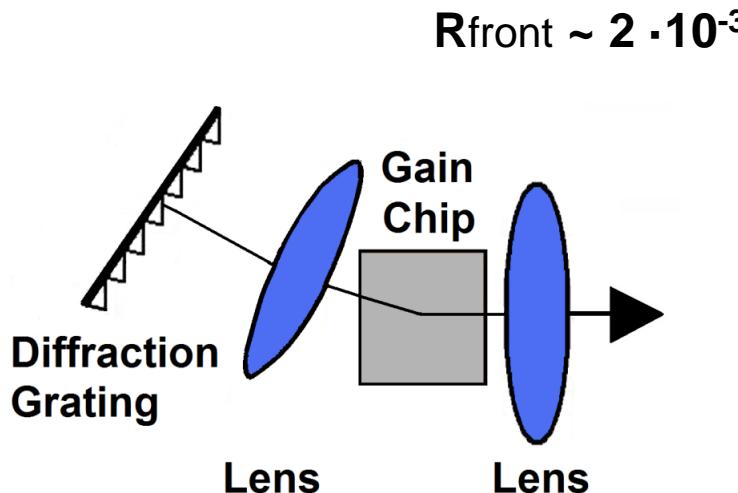
E.U. Rafailov et al., Nature Photonics, 1, p. 395, 2007

Low light absorption and minimal scattering in human tissue in 1 – 1.3 μm range

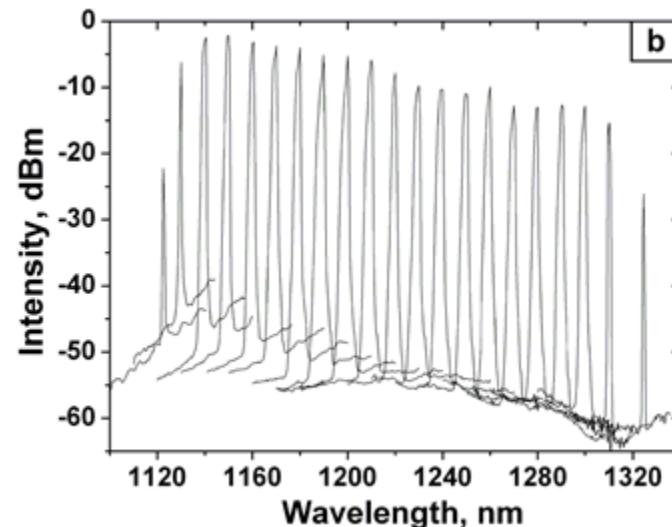
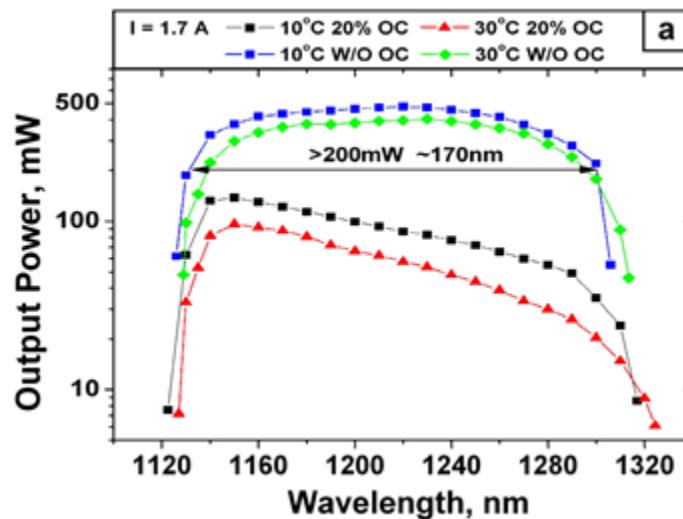
InAs/GaAs QD tunable laser

High-power CW external cavity InAs/GaAs quantum-dot diode laser with a tuning range of **202 nm** (between **1122 nm** and **1324 nm**)

- 4 mm length, 5 μm wide waveguide
- 10 layers InAs QDs, grown on GaAs substrate
- waveguide angled at 5°
- facets AR coated: Rangled < 10^{-5}

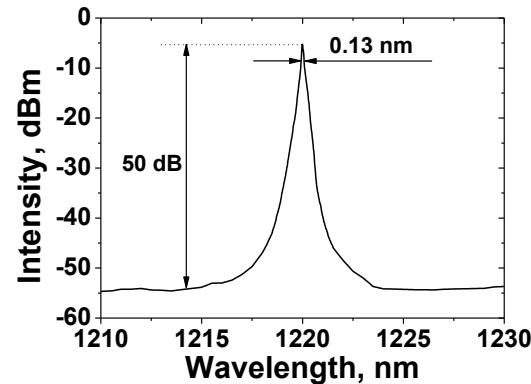


Spectral characteristics



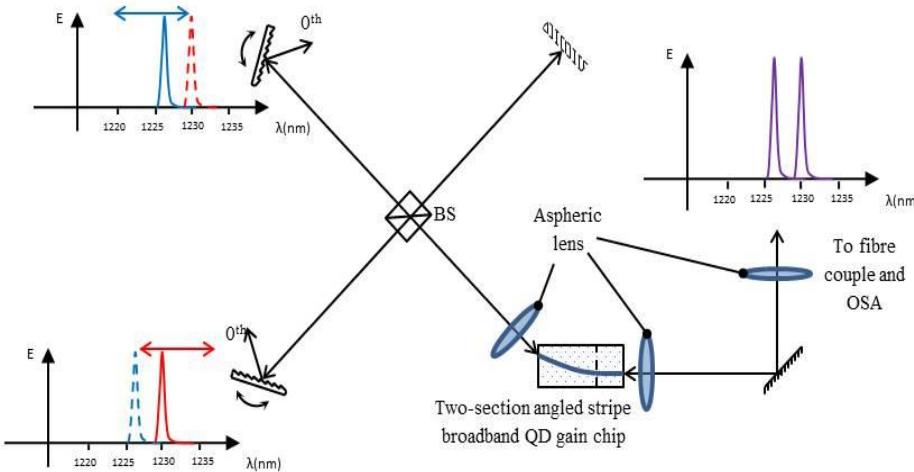
A tuning range of **202nm** was achieved with the QD laser.

Max Output Power @ 10°C , 1700mA:
W/O OC **500 mW ($\lambda=1220\text{nm}$)**
20%OC **140 mW ($\lambda=1150\text{nm}$)**



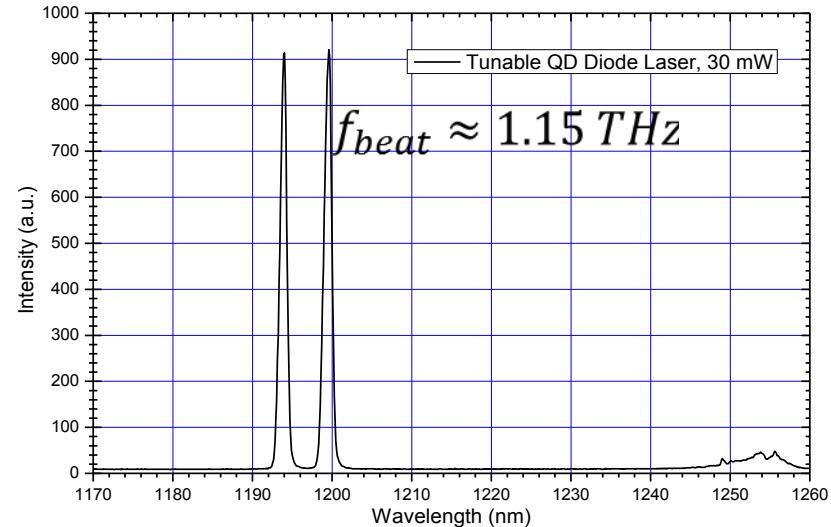
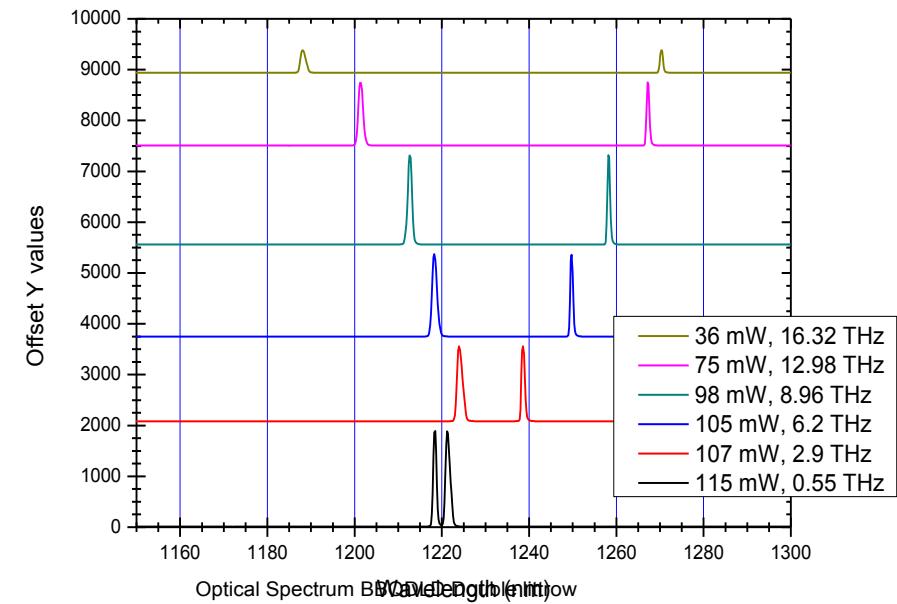
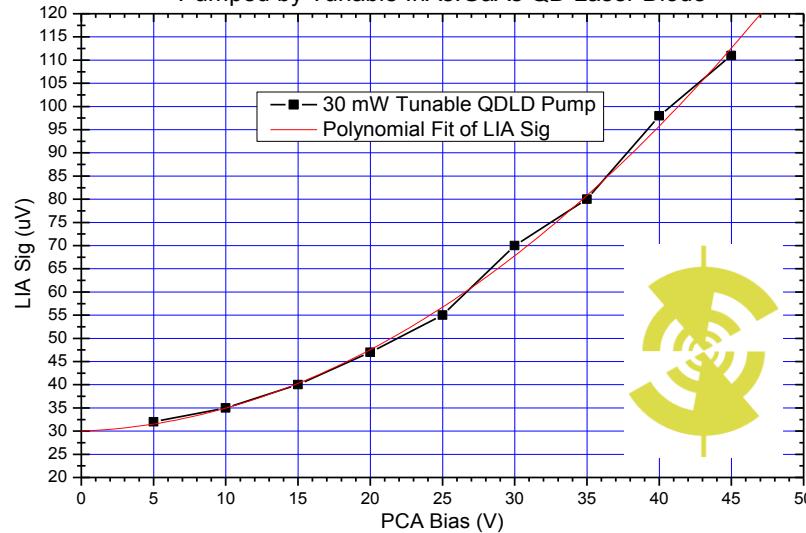
The results obtained show that the tuning range is mostly enhanced on the **blue side** of the spectrum for lower temperatures and higher pump currents, whereas reducing the cavity losses assists in the enhancement of the tuning range on the **red side** of the spectrum.

Spectral characteristics



Broadly tunable CW LD

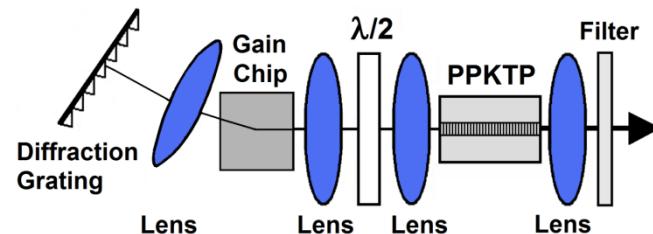
THz Output Trend, 25-layer QD Structure with 5um Gap Antenna
Pumped by Tunable InAs:GaAs QD Laser Diode



SHG in a periodically poled KTP waveguide

PPKTP crystal used in this work

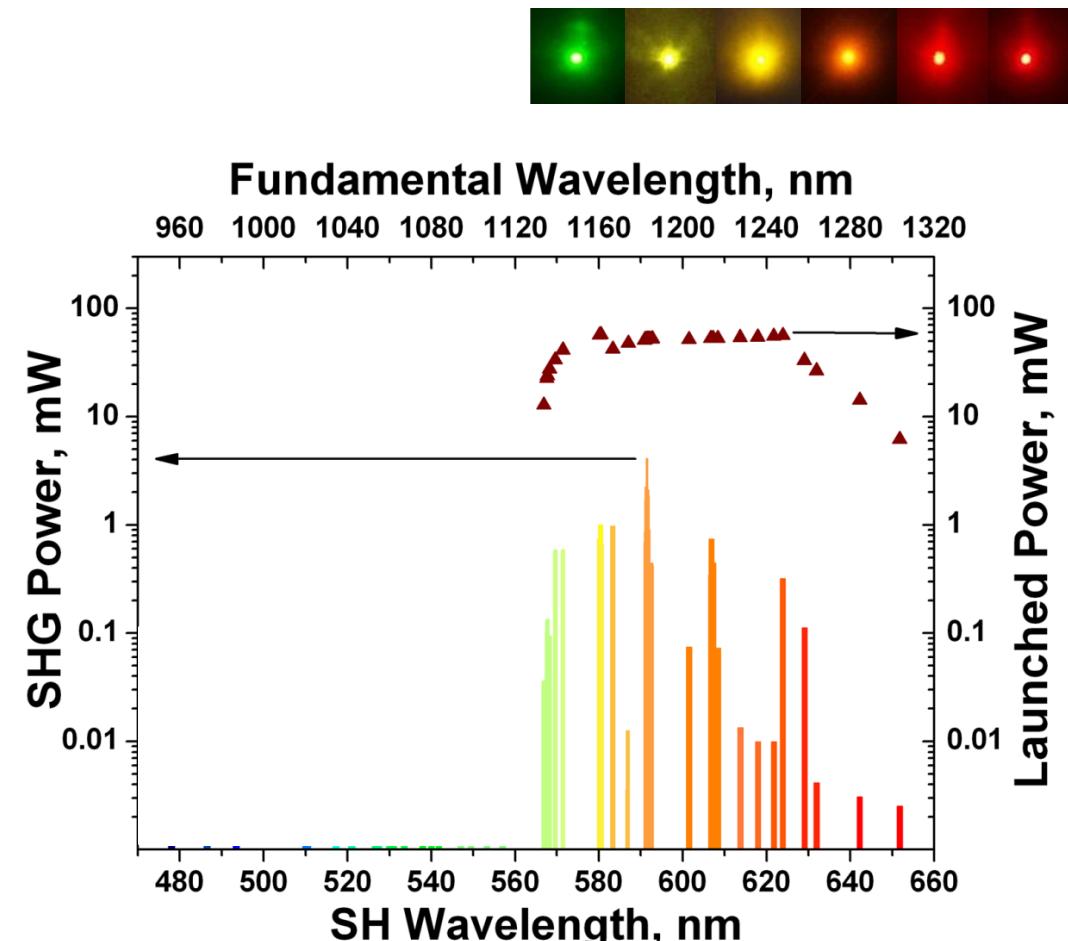
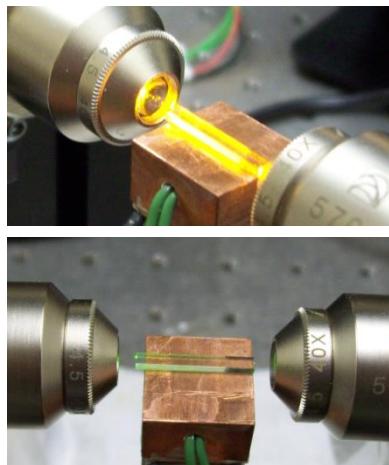
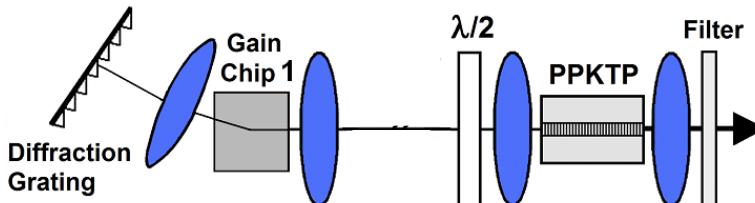
- 16 mm length
- facets not AR coated
- waveguide with cross-sectional area of $\sim 4 \times 4 \mu\text{m}^2$
- periodically poled for SHG at $\sim 1183 \text{ nm}$
(poling period $\sim 12.47 \mu\text{m}$)
- refractive index step $\Delta n \approx 0.01$



Both the pump laser and the crystal were operating at room temperature

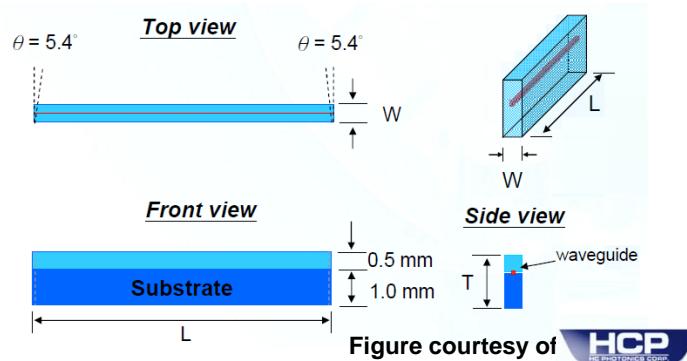


Blue-to-Red tunable SHG



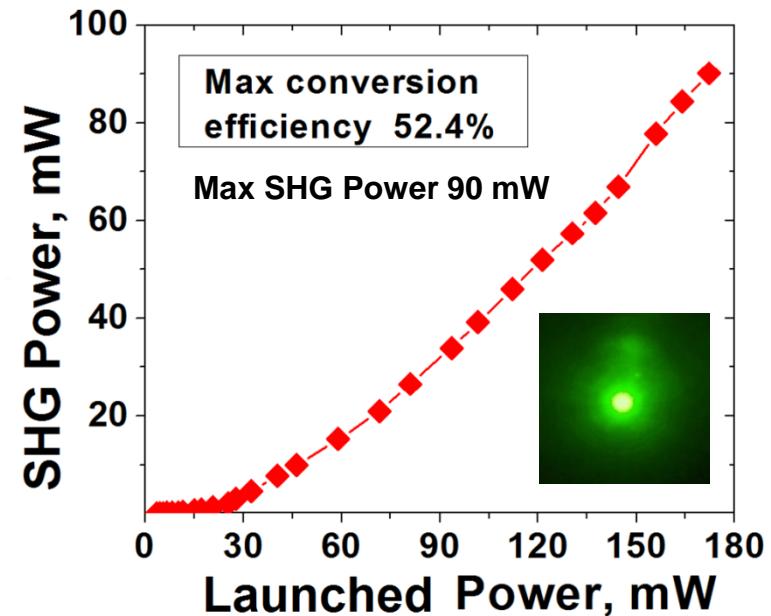
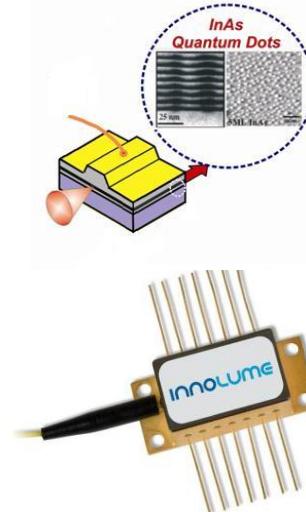
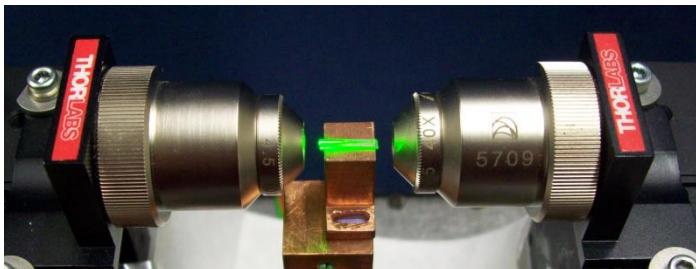
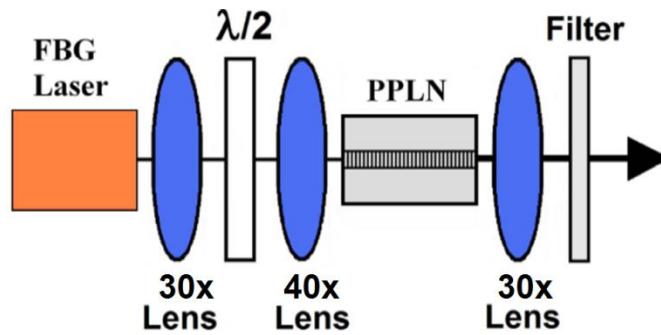
Dependence of SHG and launched pump power on wavelength over **567 nm – 652 nm** wavelength range

SHG at 561 nm from a PPLN waveguide

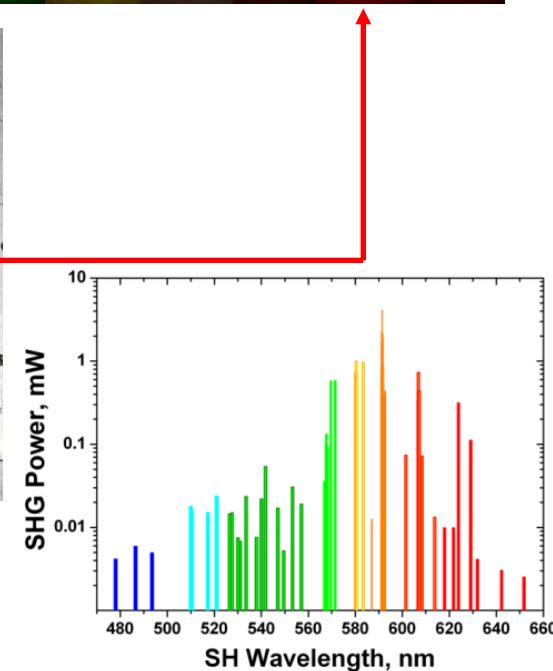
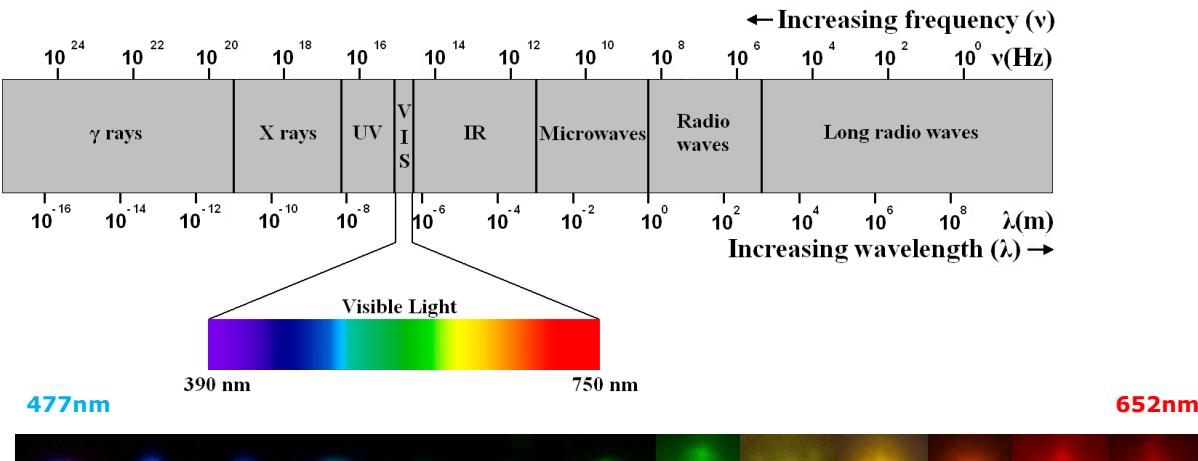


5% MgO-doped Y-cut congruent lithium niobate

- Dimensions: 10 mm (L) x 0.5 mm (W) x 1.5 mm (T)
- Facets optically polished at $\sim 5.4^\circ$
- AR coating at 1122 nm ($R < 0.5\%$) & at 561 nm ($R < 1\%$) on both input/output facets
- Cross-sectional area of the waveguide is $\sim 4 \times 5 \mu\text{m}^2$



Compact visible laser sources

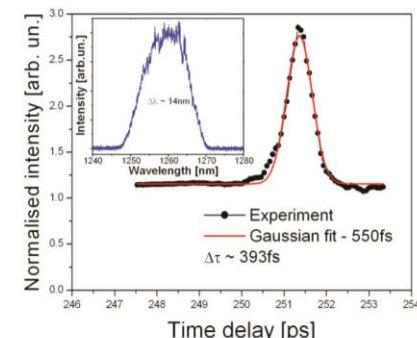
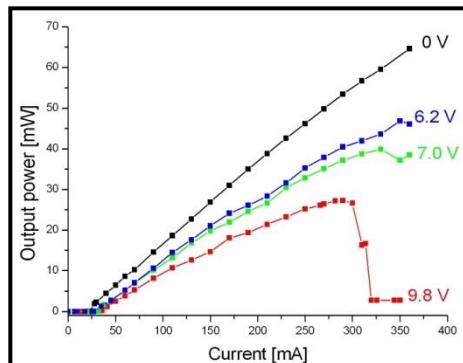


Applications

- Fluorescence microscopy
- Spectroscopy
- Medical Biotechnology
- Cell-surgery
- Dermatology (e.g. photodynamic therapy of cancer)
- Cosmetic treatments (tattoo removal, hair removal)
- Ophthalmology
- Flow cytometry
- Dentistry



Mode-locked QD laser



Shortest pulse duration

$Dt < 400\text{fs}$

Highest peak power

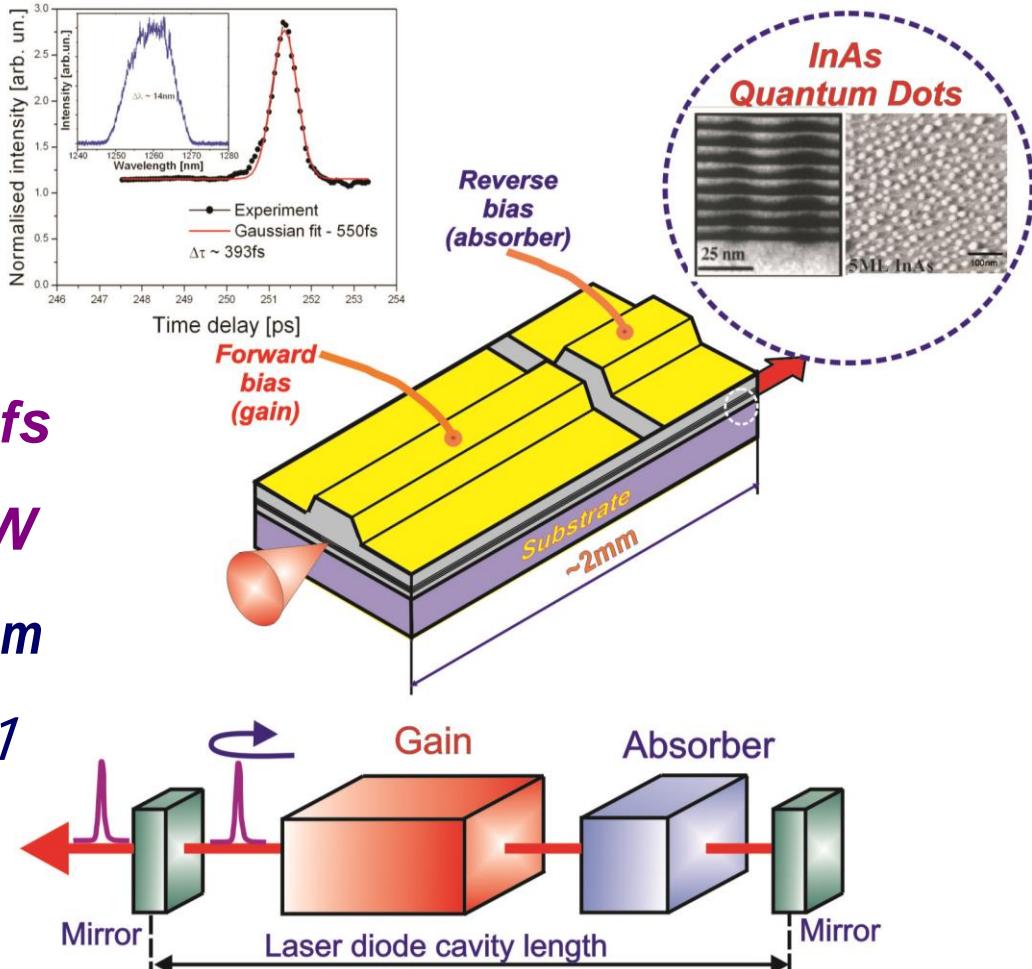
$P_{\text{peak}} \sim 3\text{W}$

Wavelength bandwidth

$D\lambda \sim 15\text{nm}$

Time bandwidth product

$Dt Dn \sim 1$



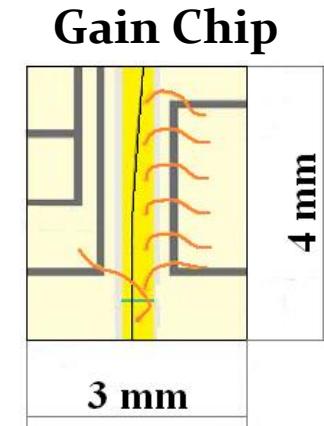
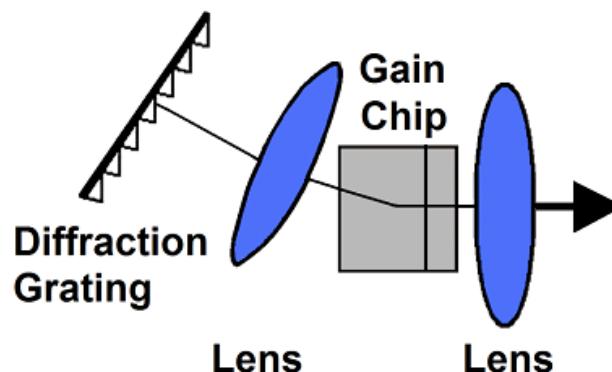
E.U. Rafailov et al., Appl. Phys. Lett. 87, p. 081107, 2005

E.U. Rafailov et al., Nature Photonics, 1, p. 395, 2007

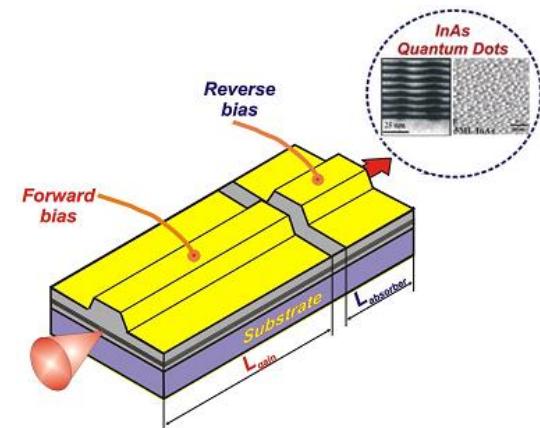
InAs/GaAs QD mode-locked tunable laser

- 10 non-identical InAs QD layers, grown on GaAs substrate
- 4 mm length, 800 μm saturable absorber
- 6 μm wide waveguide
- waveguide angled at 7°
- facets AR coated: Rangled < 10^{-5}

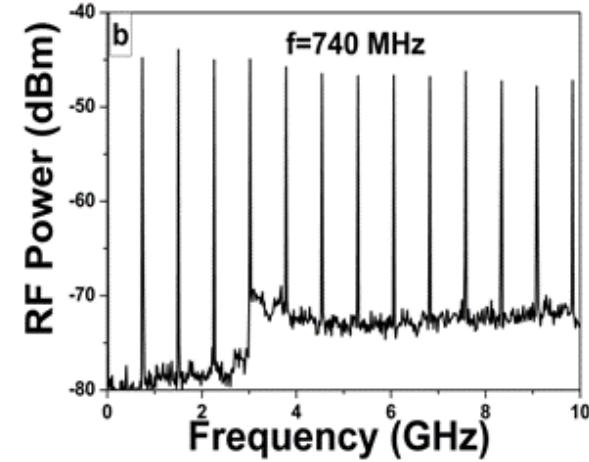
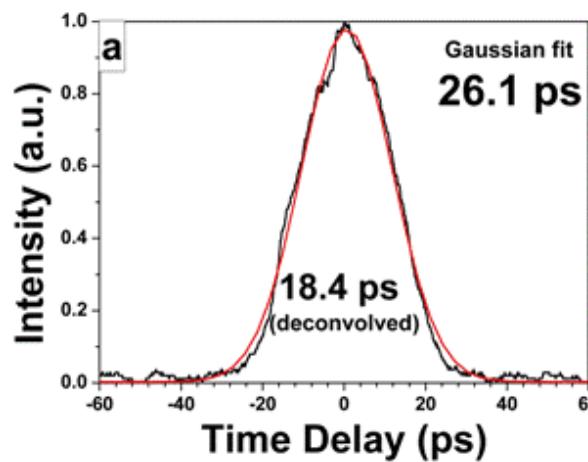
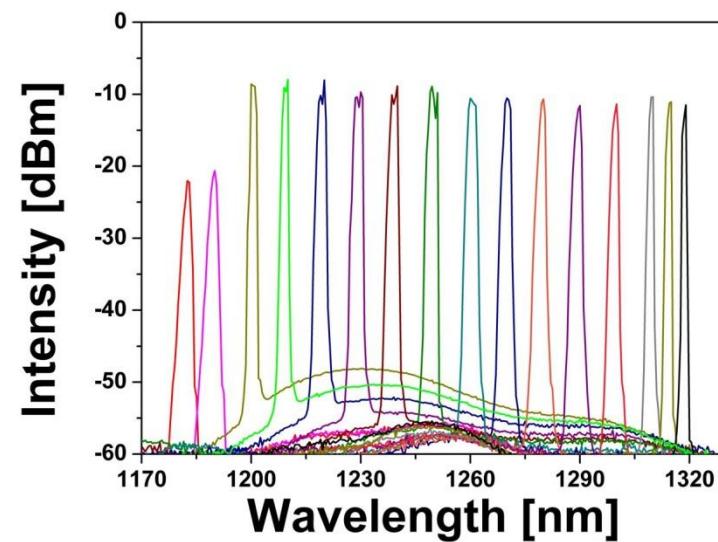
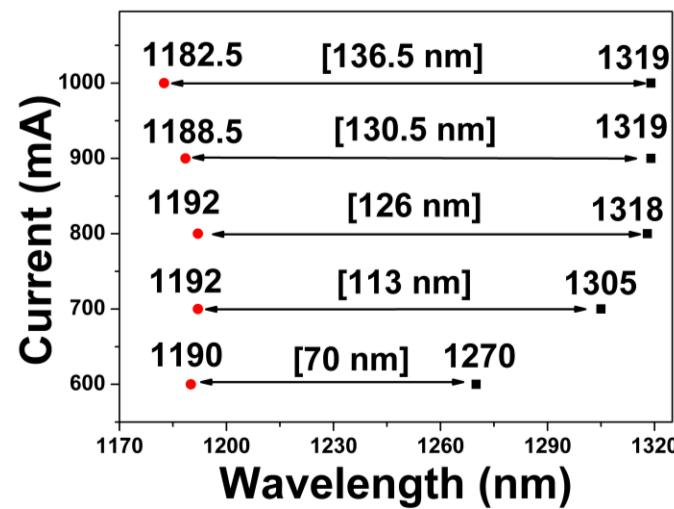
$$R_{\text{front}} \sim 10^{-2}$$



innolume



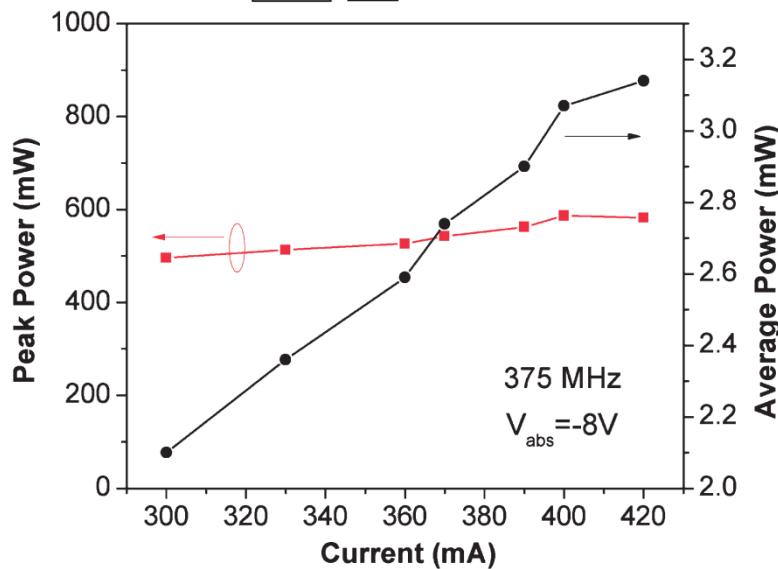
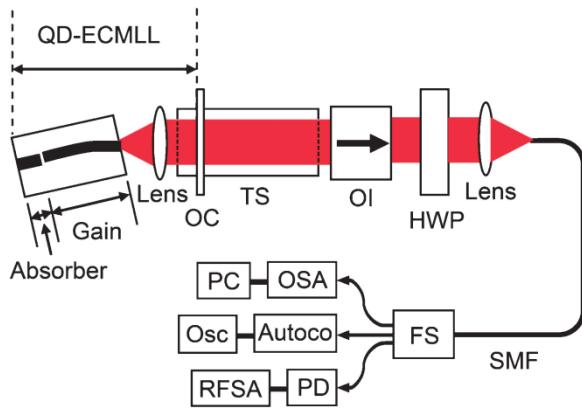
InAs/GaAs QD mode-locked tunable laser



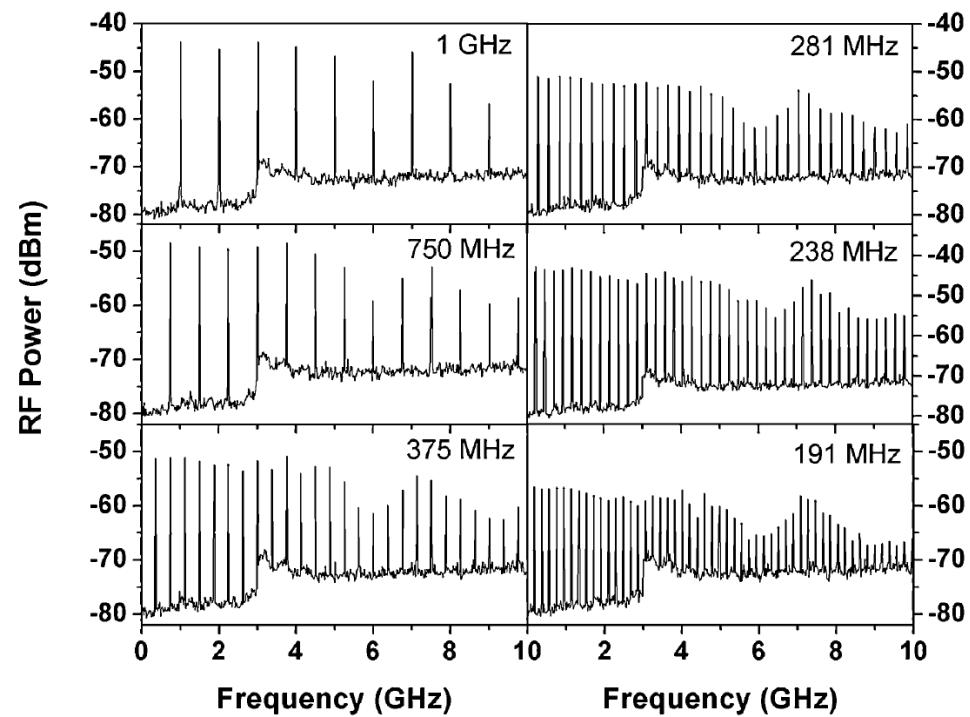
Operating current: 1A
Reverse bias: 4V
Ppeak = 870 mW
 Δt = 18.4 ps
 λ = 1226 nm
 $\Delta\lambda$ = 1.2 nm
TBWP = 4.4

A broadly tunable high-power external cavity InAs/GaAs quantum-dot mode-locked laser with a tuning range of 137 nm (1182 nm – 1319 nm) is demonstrated

Broad Repetition-Rate Tunable QD-ECMLL

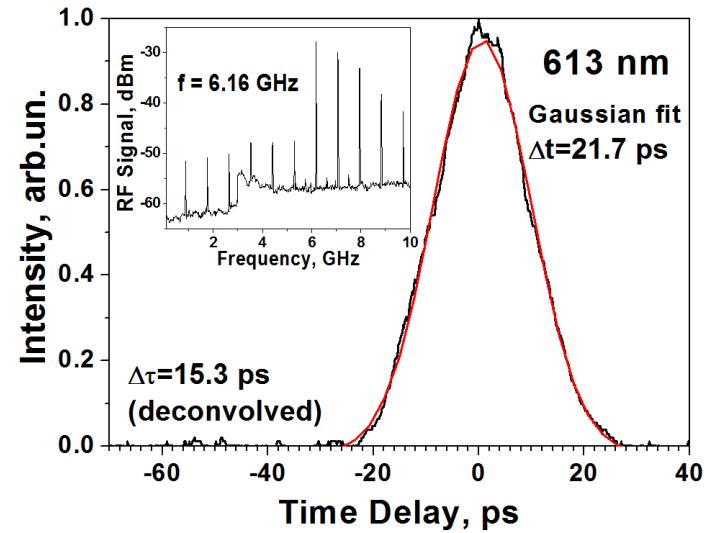
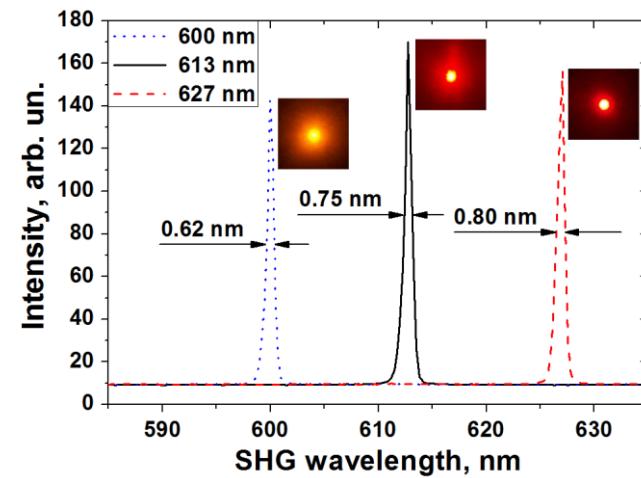
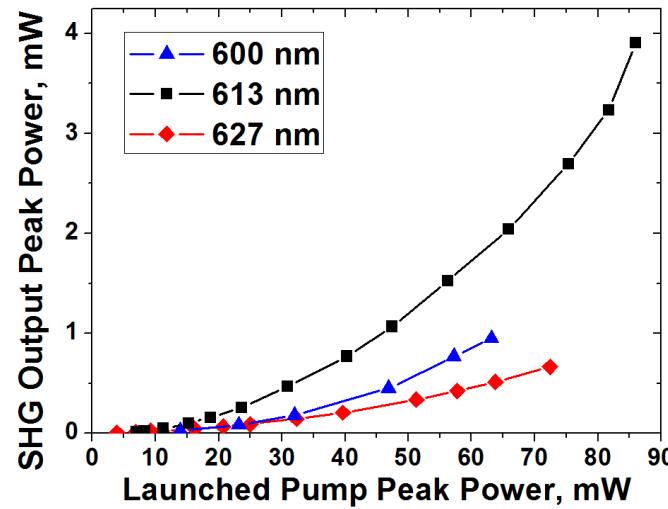
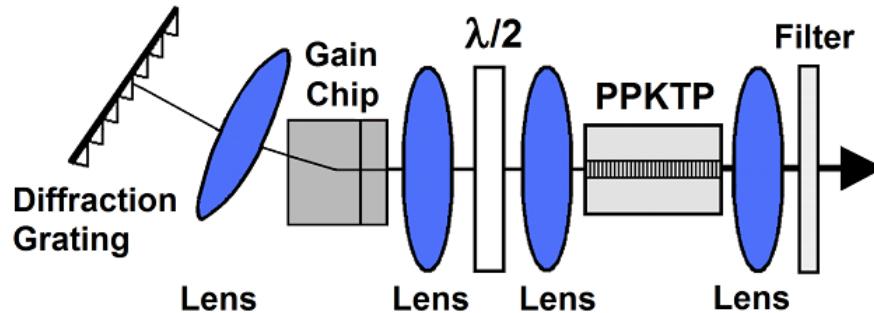


The peak power remains nearly constant under certain operation conditions (especially at a low gain current and a high reverse bias), with different pulse repetition rates

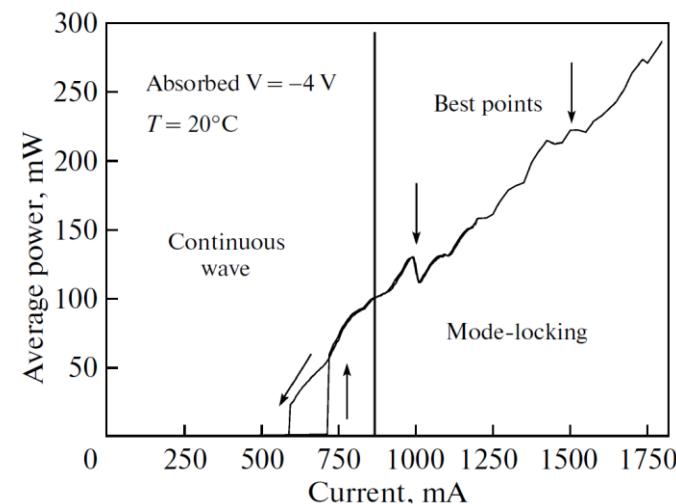
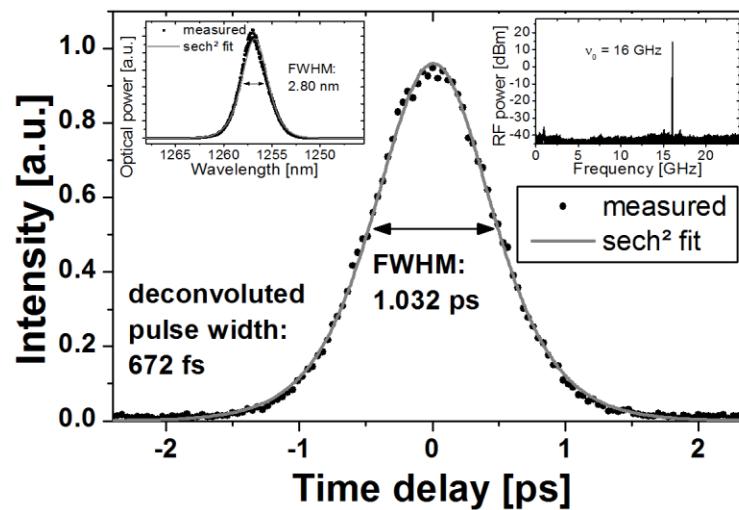
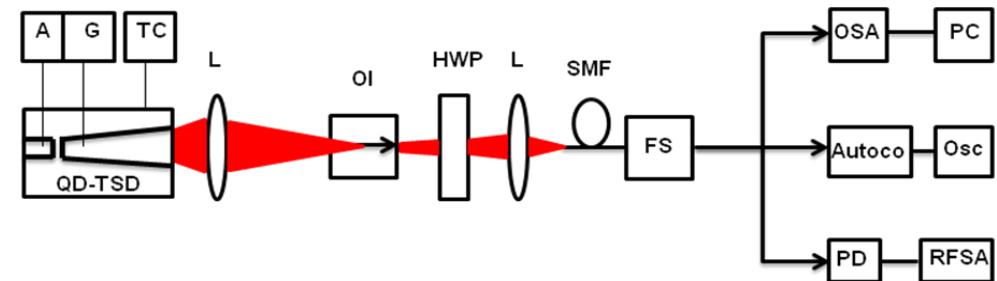
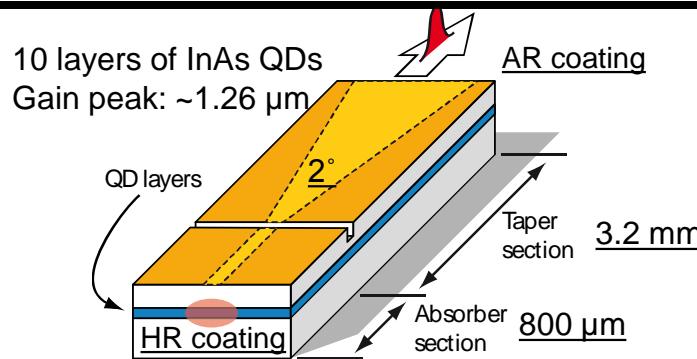


Broad repetition-rate tunable QD-ECMLL demonstrated frequency tuning range from **1 GHz** to a record-low value of **191 MHz** (The corresponding total optical cavity length varied from 15 to 78.5 cm)

Orange-to-Red tunable picosecond SHG

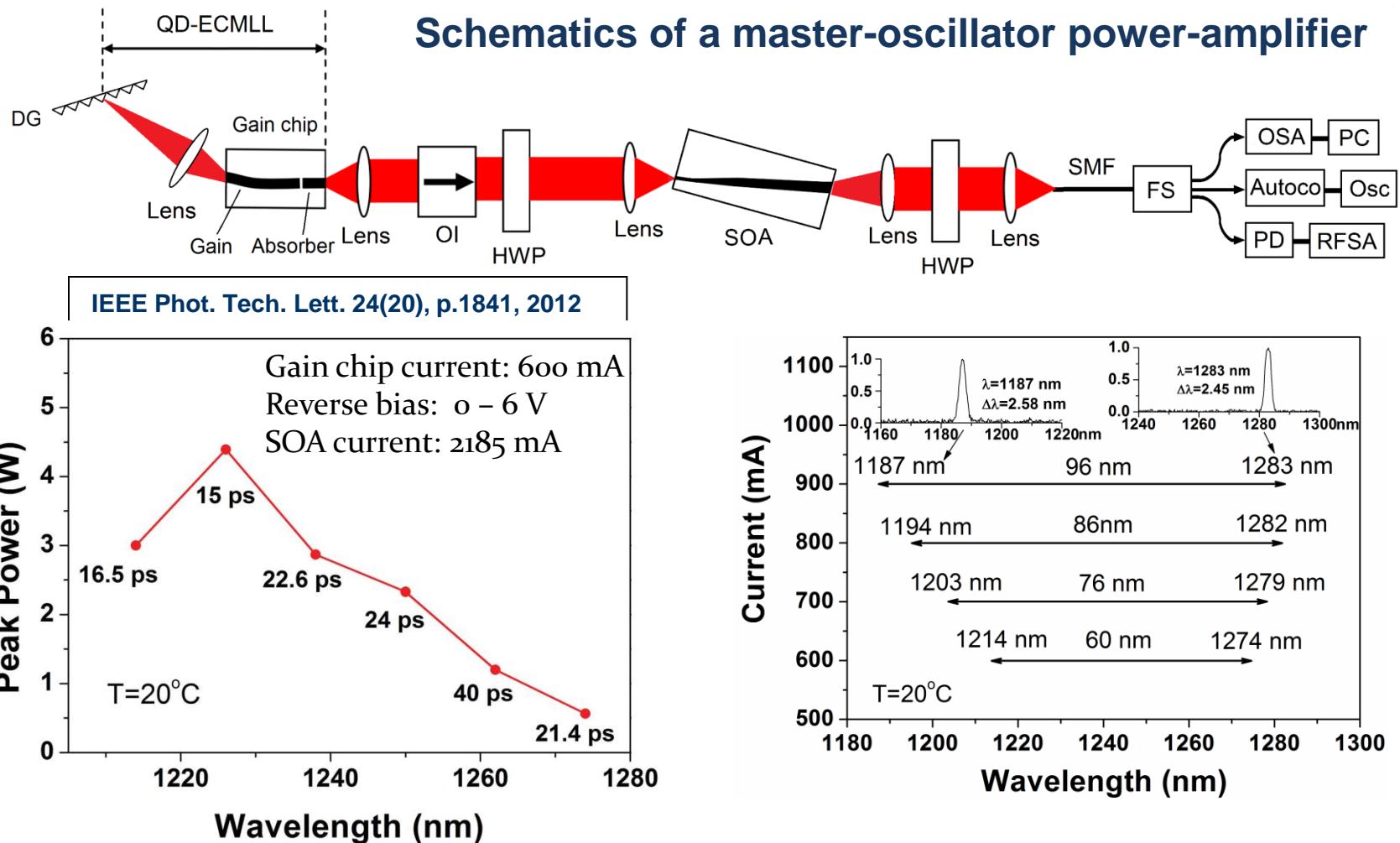


QD Tapered Lasers



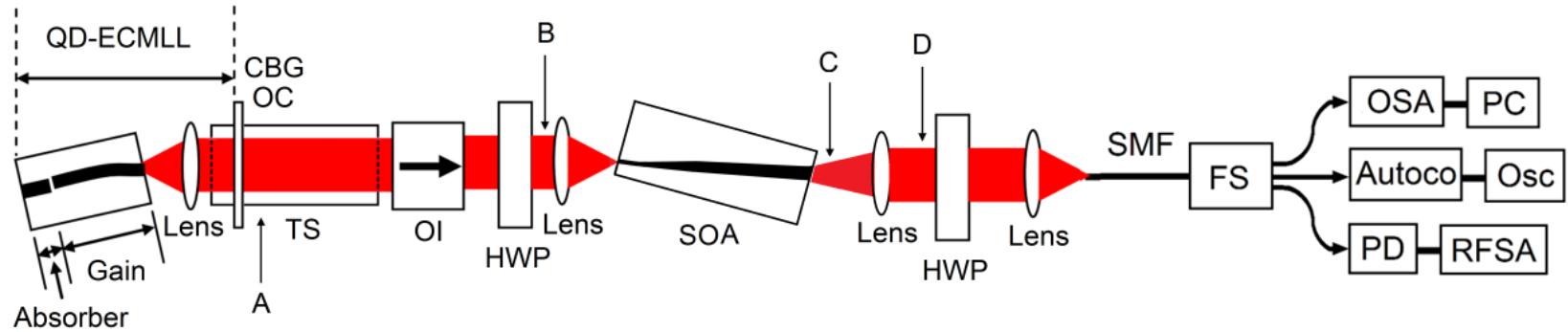
$P_{\text{aver}} = 288 \text{ mW}; \quad P_{\text{peak}} = 17.7 \text{ W}; \quad \lambda \sim 1260 \text{ nm};$
 $\Delta t \sim 672 \text{ fs}; \quad \Delta\lambda = 2.8 \text{ nm}; \quad f \sim 16 \text{ GHz}$

Broadly tunable QD-based MOPA



Demonstration of a **96-nm** tunable (between **1187 nm** and **1283 nm**) MOPA picosecond optical pulse system formed by an QD-ECMLL and a tapered SOA with **4.39-W** peak power under fundamental mode-locked operation

High-power QD-based MOPA



Gain Chip

- 10 layers InAs QDs, grown on GaAs substrate
- 4 mm length, 800 μm saturable absorber
- 6 μm wide waveguide
- waveguide angled at 7°
- front facet AR coated: R angled < 10^{-5}
- back facet HR coated: R ~ 95%

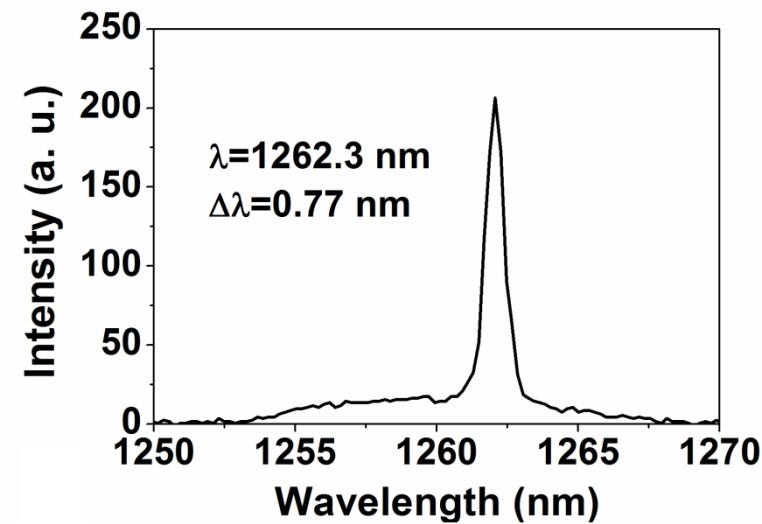
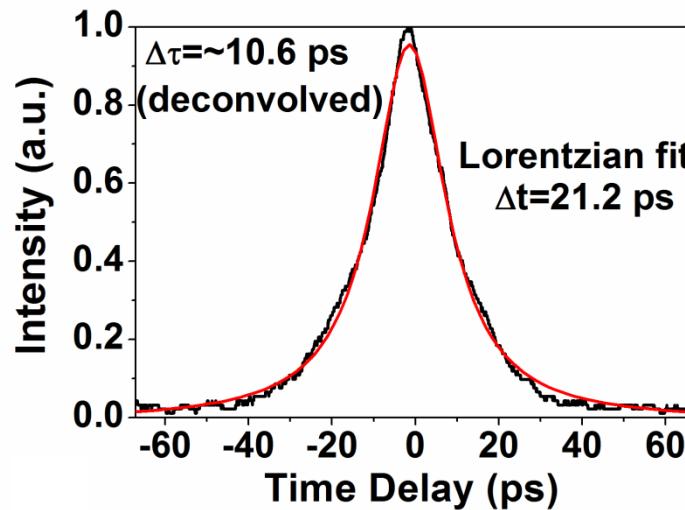
SOA

- 10 layers InAs QDs, grown on GaAs substrate
- 6 mm length
- waveguide width changes from 14 μm to 80 μm
- facets AR coated: R ~ 10^{-5}

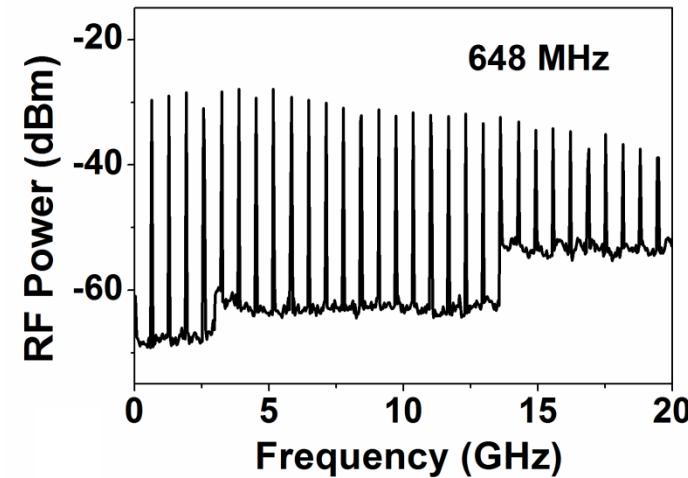
Chirped Bragg grating (CBG)

- center wavelength ~ 1262 nm
- reflectivity ~12-15%

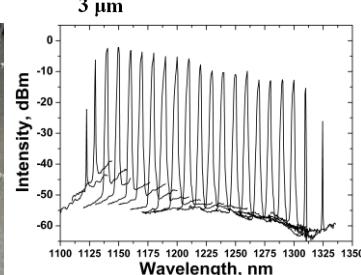
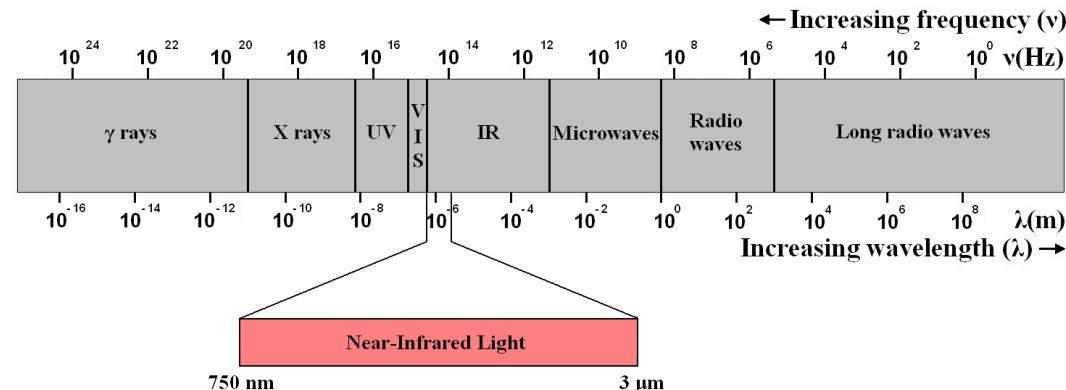
High-power QD-based MOPA



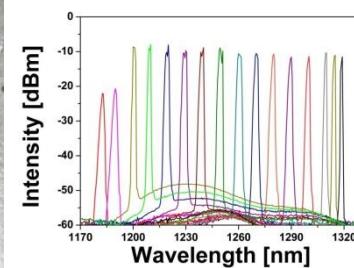
Gain chip current: **200mA**
Reverse bias: **4V**
SOA current: **2.5A**
Ppeak = **30.3 W (42 W)***
 $\Delta t = 10.6 \text{ ps}$
Repetition rate: **648 MHz**
 $\lambda = 1262.3 \text{ nm}$



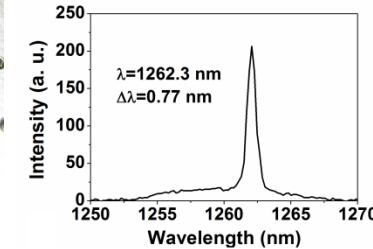
Compact QD laser sources



1122 nm – 1324 nm
Up to 500 mW in CW



1182 nm – 1319 nm
Up to 4.39 W pulsed
(1.3GHz, 15-20ps)



Up to 30.3 W pulsed
(648MHz, 10.6ps)
Down to 191 MHz rep. rate
672 fs pulse duration

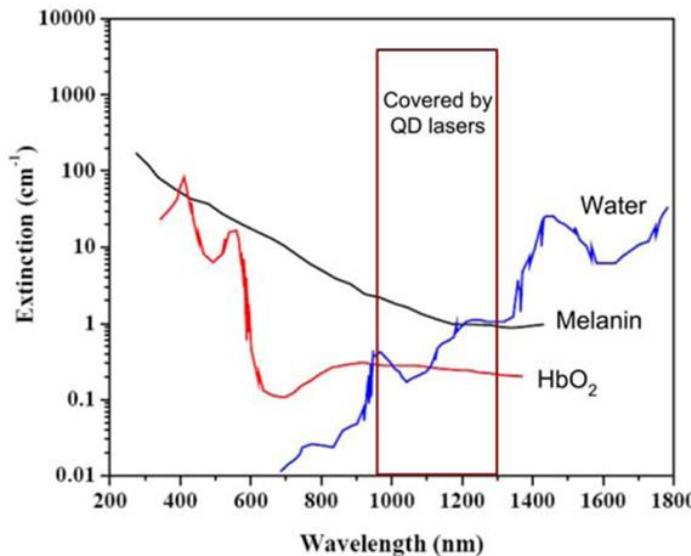
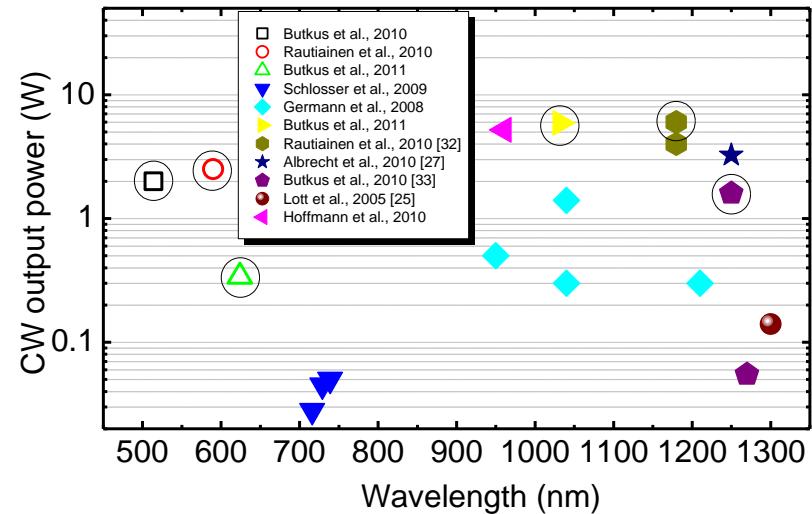
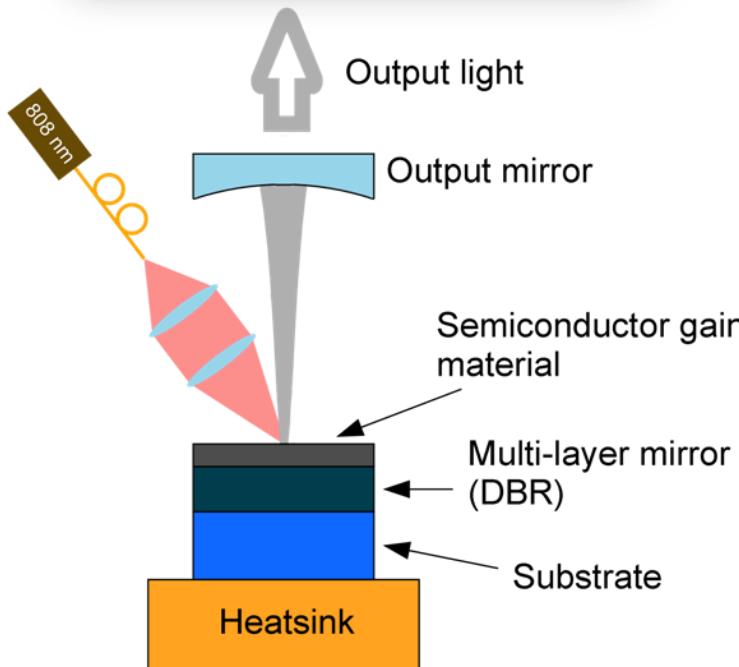
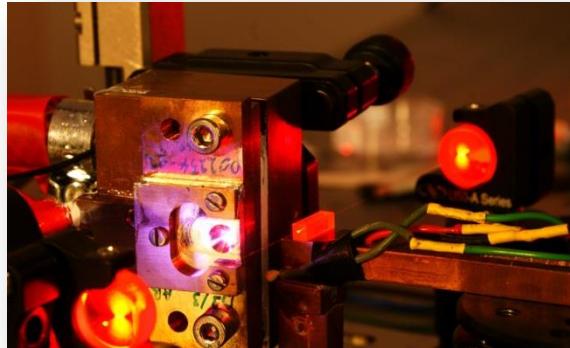
Applications

- Fluorescence microscopy
- Spectroscopy
- Optical coherence tomography
- Cell-surgery
- Dermatology (e.g. photodynamic therapy of cancer)
- Cosmetic treatments (tattoo removal, hair removal)
- Ophthalmology
- Dentistry
- Blood analysis
- Frequency-conversion



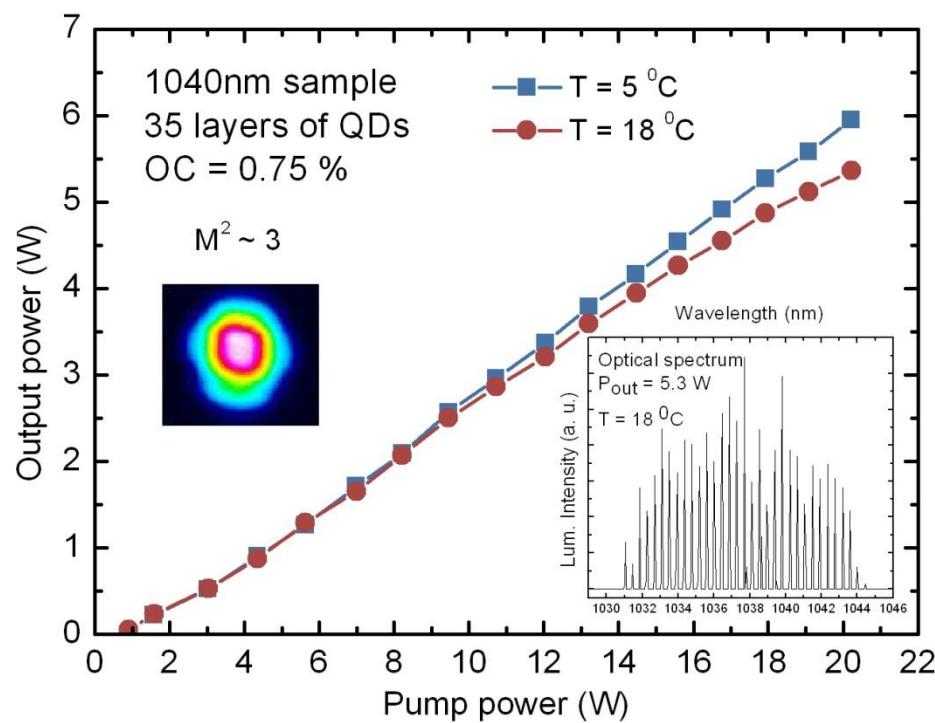
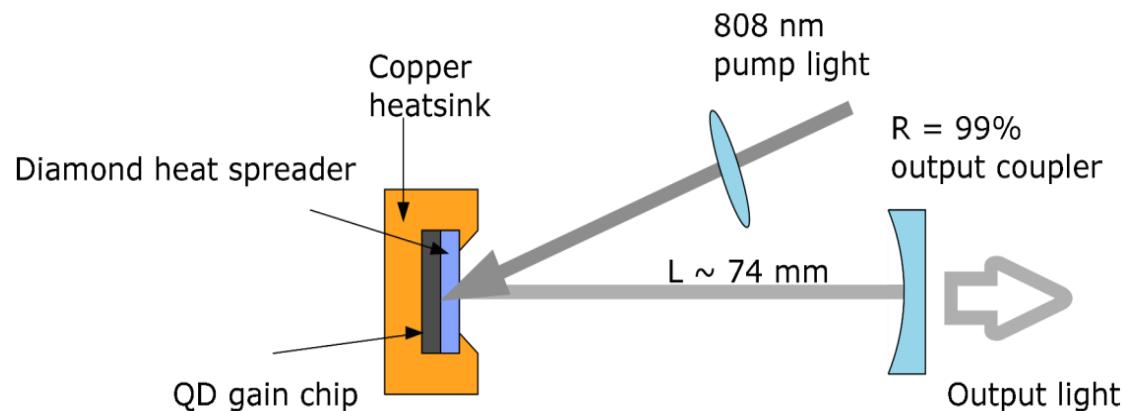
QD Semiconductor Disk Laser (SDL)

Vertical External Cavity Surface Emitting Laser (VECSEL)



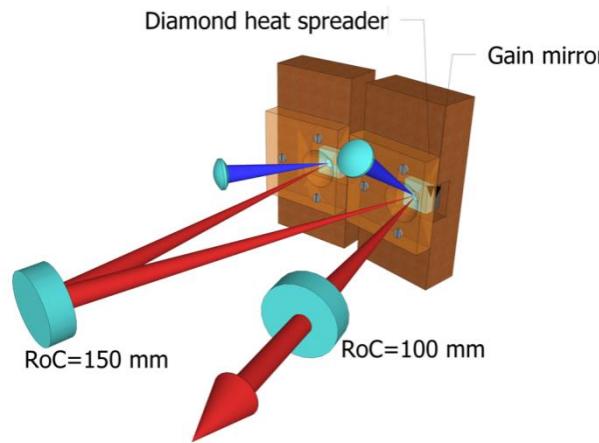
Low light absorption and minimal scattering
in human tissue in 1 – 1.3 μm range

6 W (8W*) CW from QD gain at 1040nm

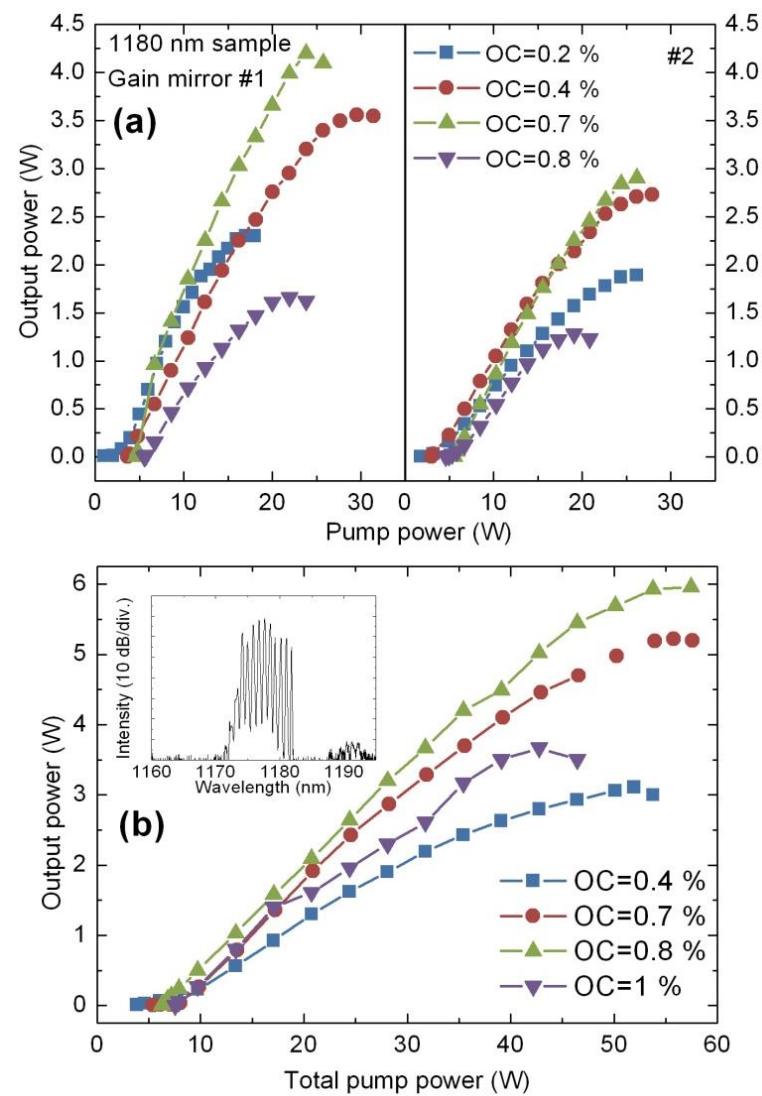


6 W CW from QD gain at 1180nm

New design with 39 QD-layers:
achieve highest average output
power of a cw QD-VECSEL
operating in the $1.2\text{-}\mu\text{m}$ spectral
region



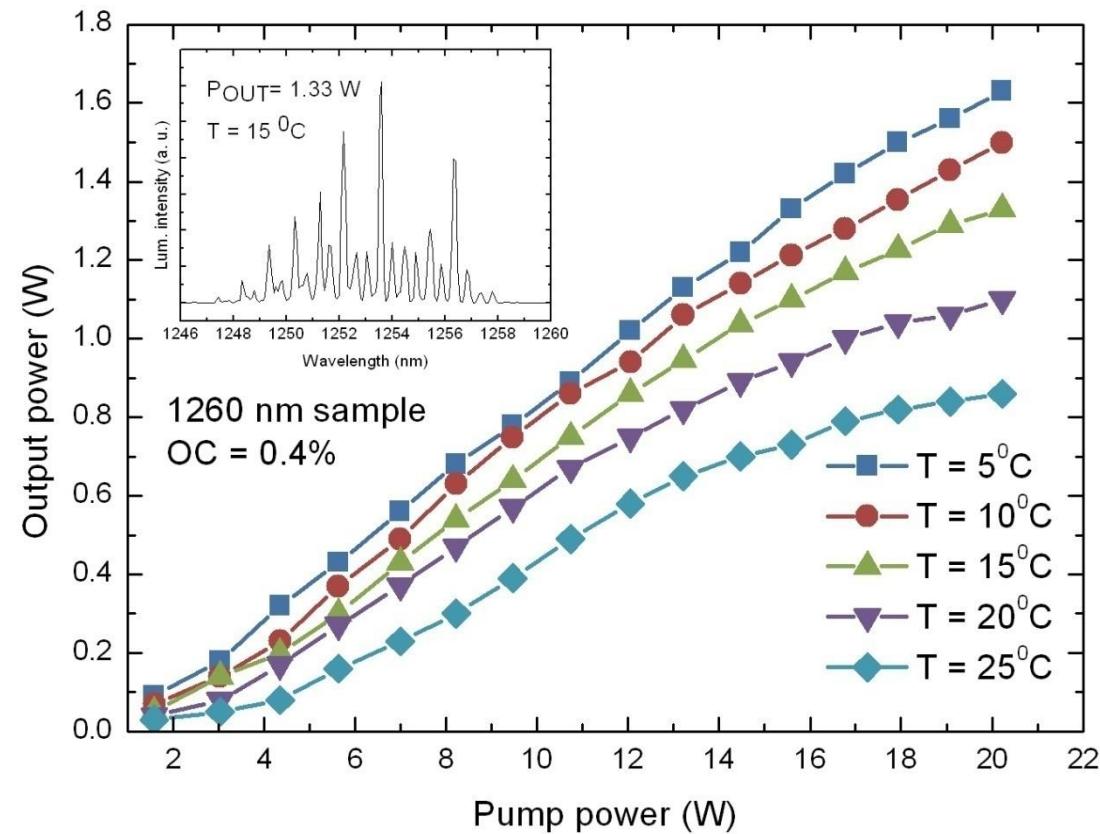
Single gain device $P_{\max} > 4 \text{ W CW}$
Dual gain device $P_{\max} > 6 \text{ W CW}$



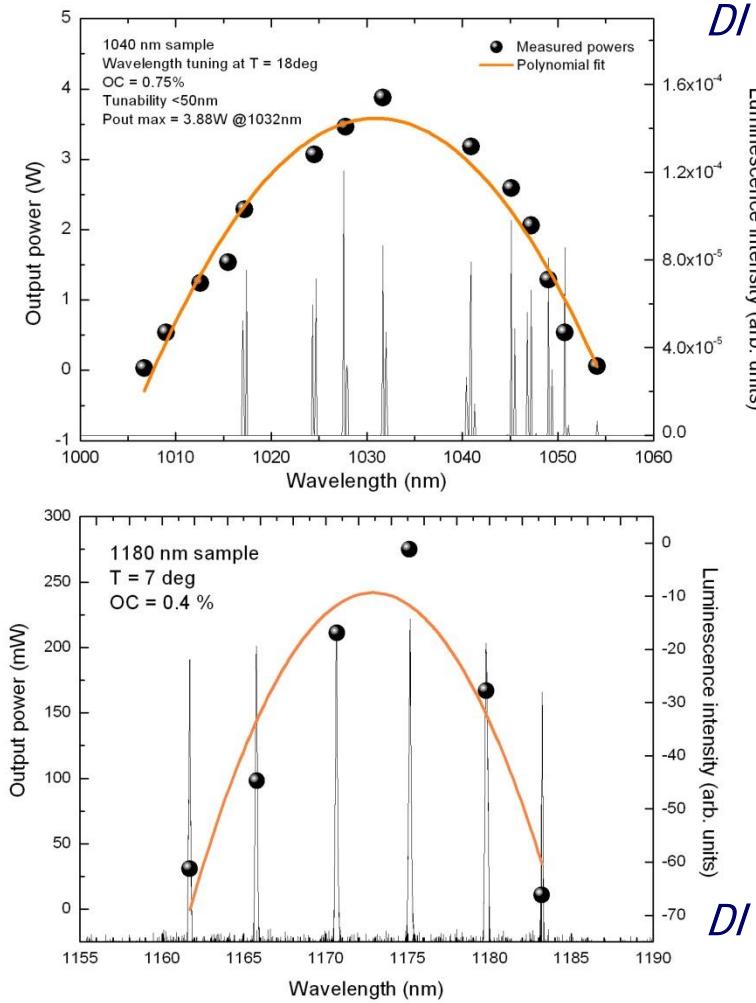
1.6 W CW from QD gain at 1260nm

New design with 39 QD-layers: achieve highest average output power of a cw QD-VECSEL operating in the 1.26- μm spectral region

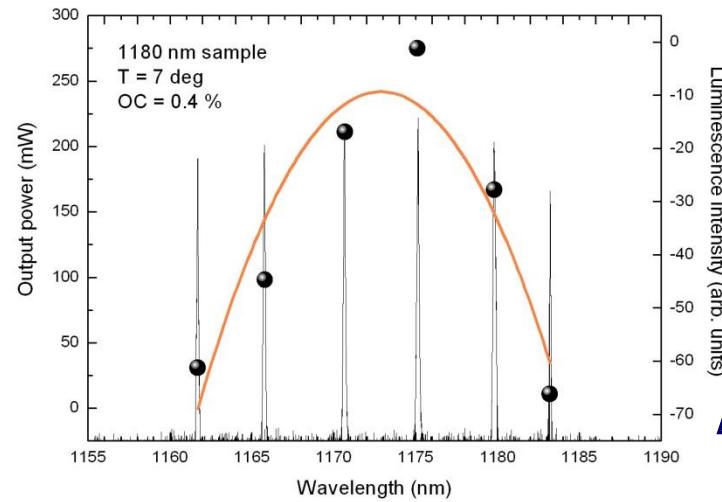
- P_{\max} 1.6 W CW
- $M^2 \sim 1.1$ up to 0.8 W



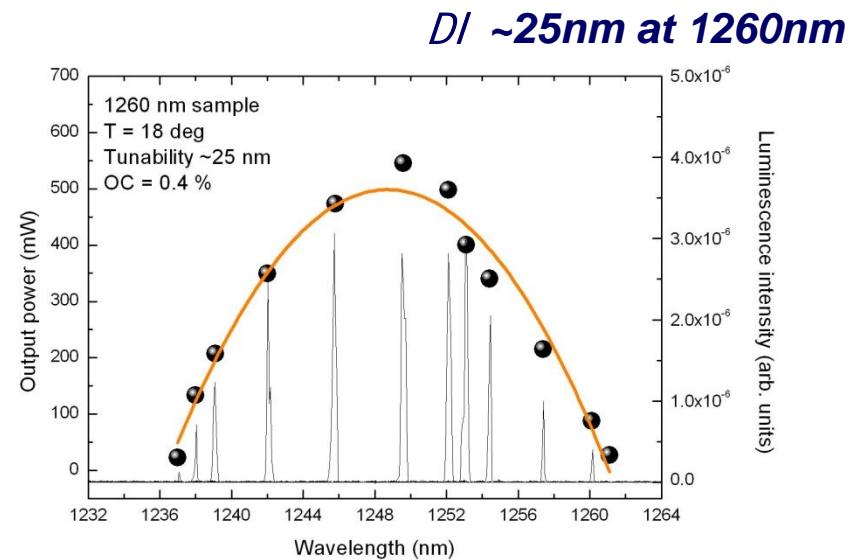
Tunable QD-SDL



DI ~60nm at 1030nm

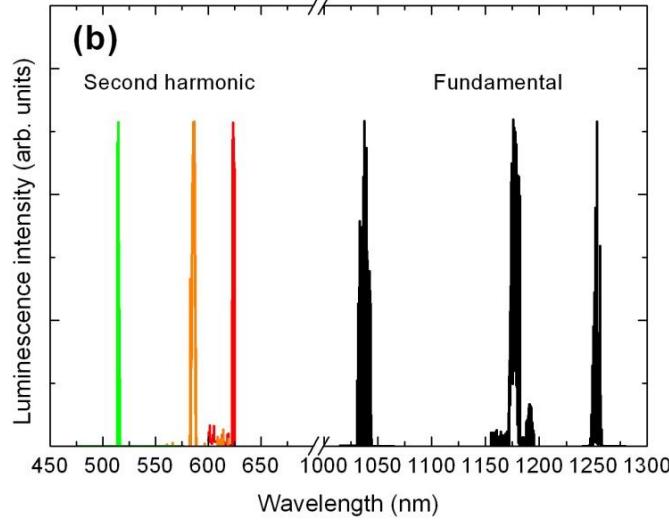
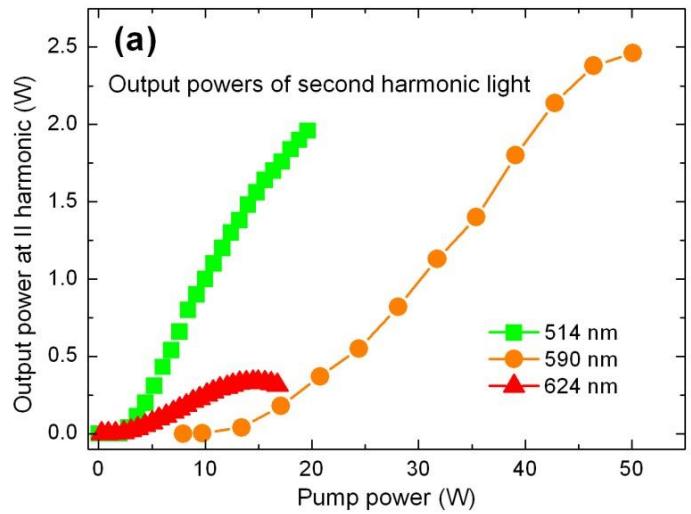


DI ~69nm at 1180nm



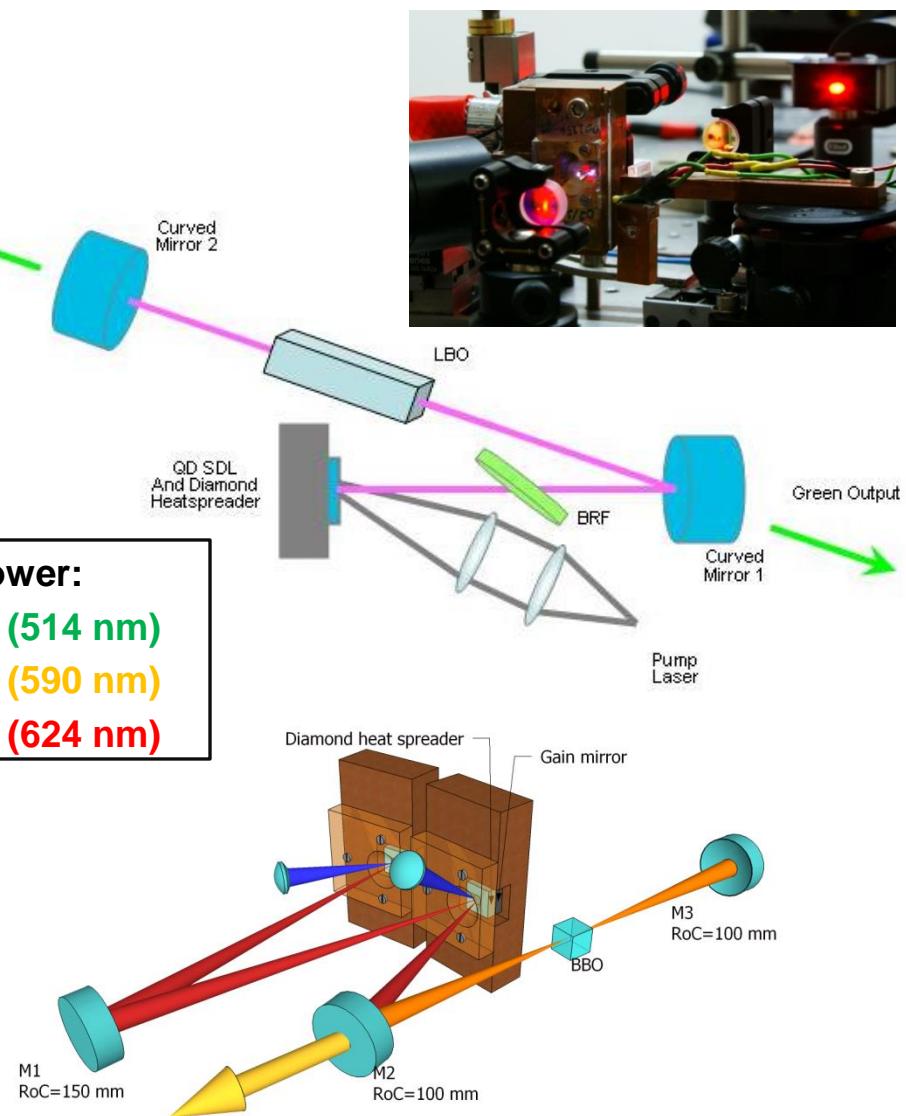
DI ~25nm at 1260nm

Intracavity SHG in QD VECSEL

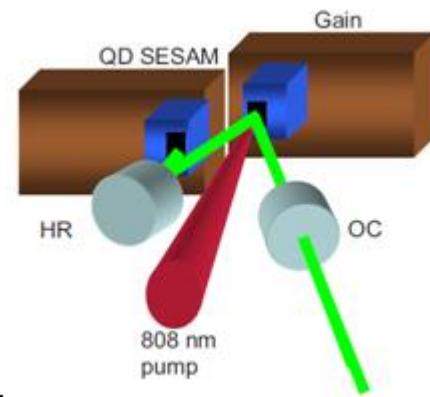
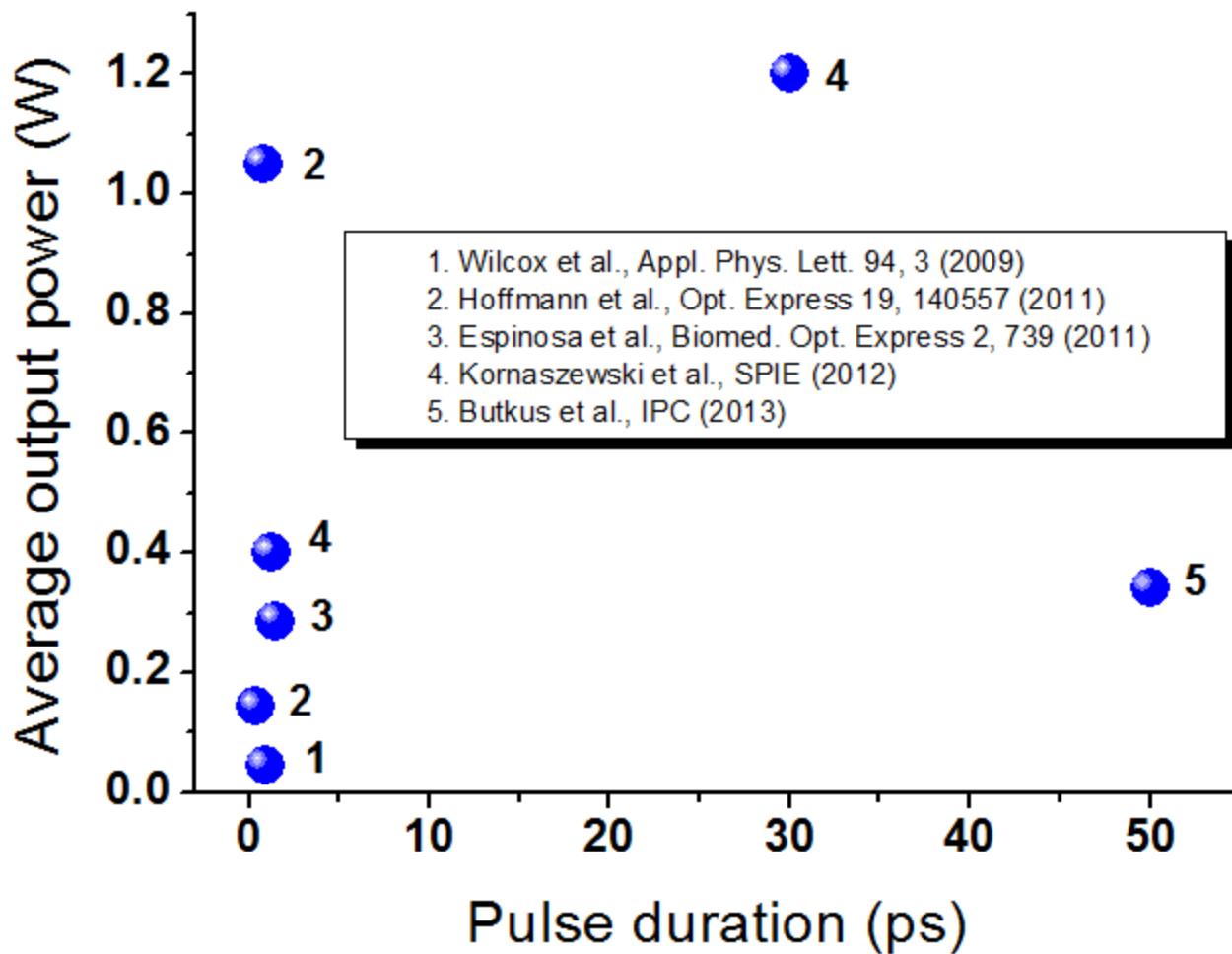


SHG power:

- 2 W (514 nm)
- 2.5 W (590 nm)
- 0.33 W (624 nm)



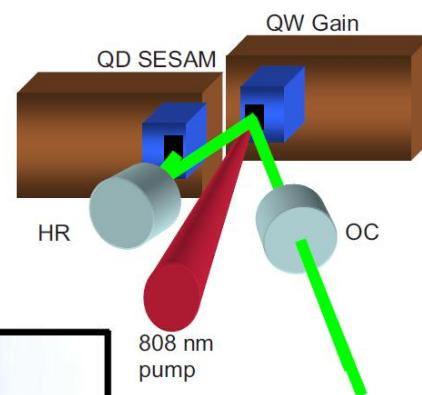
Recent development of mode-locked SDLs with QD technology



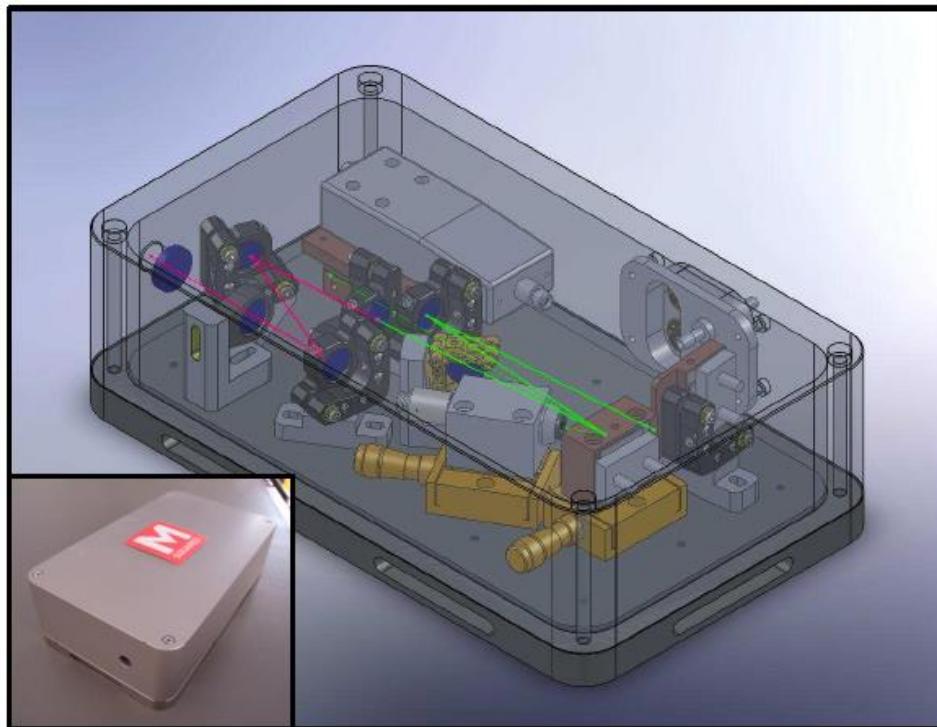
Mode-locked SDL

Mode-lock SDL with QW gain and using QD SESAM

- $\lambda = 965 \text{ nm}$
- Room temperature operation (20°C)



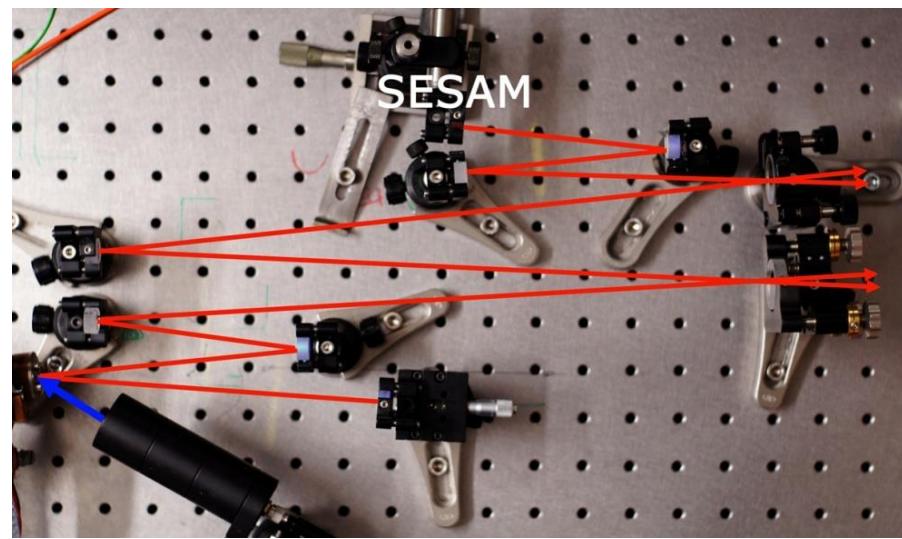
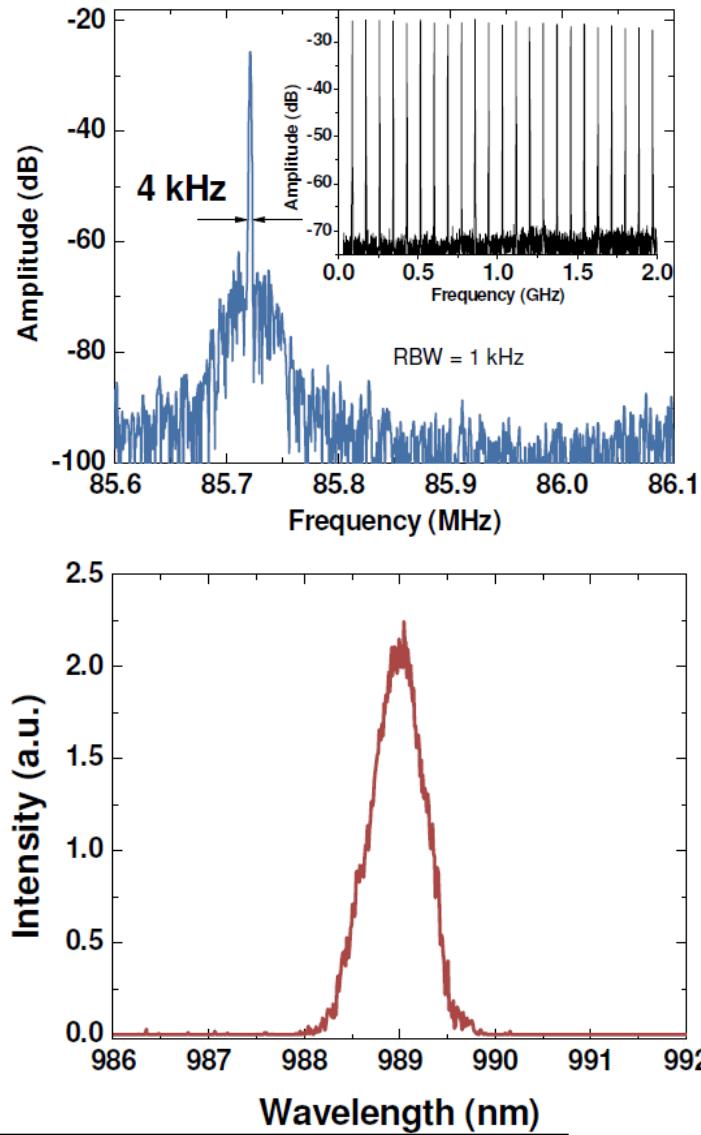
- Gain:**
- 6 layers of QW
- SESAM:**
- 5 QD layers



- Output power: **> 1 W**
- Pulse duration **< 1.5 ps**
- Repetition rate: **500 MHz**

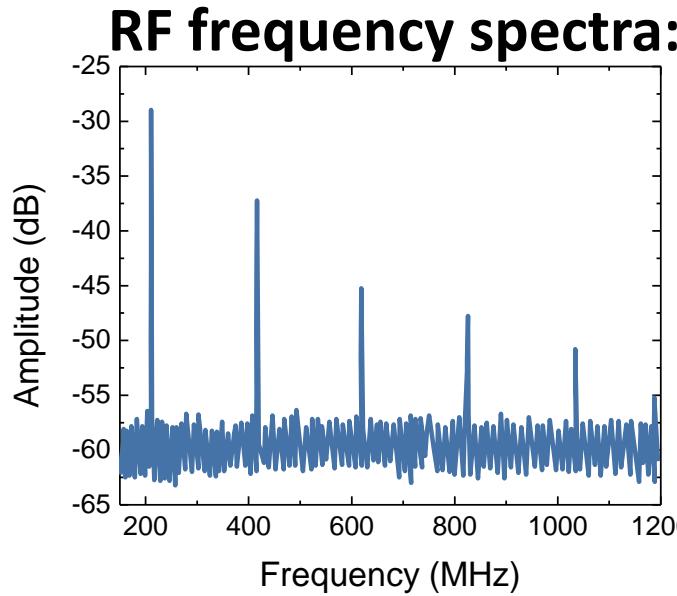


Ultra-low repetition rate mode-locked SDL

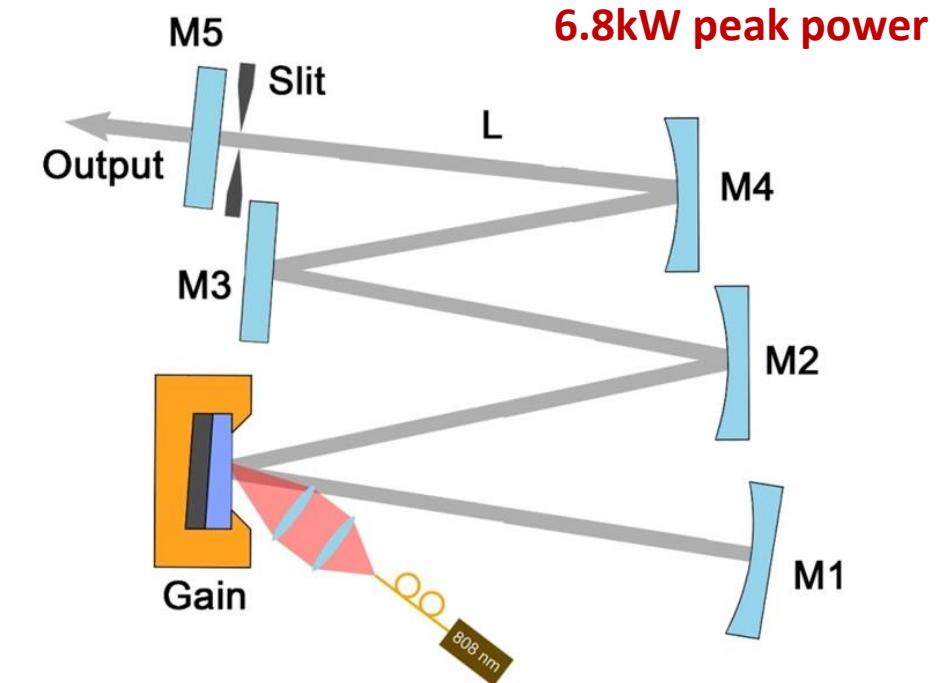
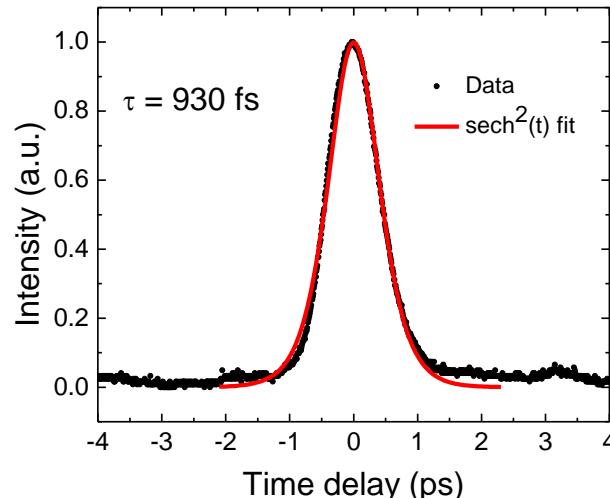


Ultra low repetition rate of **85.7 MHz** is demonstrated in mode-locked semiconductor disk laser overcoming short carrier lifetime limitations. It is shown that fundamental mode-locking in such long cavity is supported by phase-amplitude coupling.

Self-mode-locking in semiconductor lasers



Autocorrelation trace:



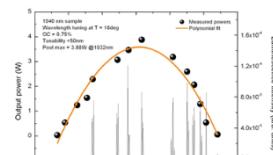
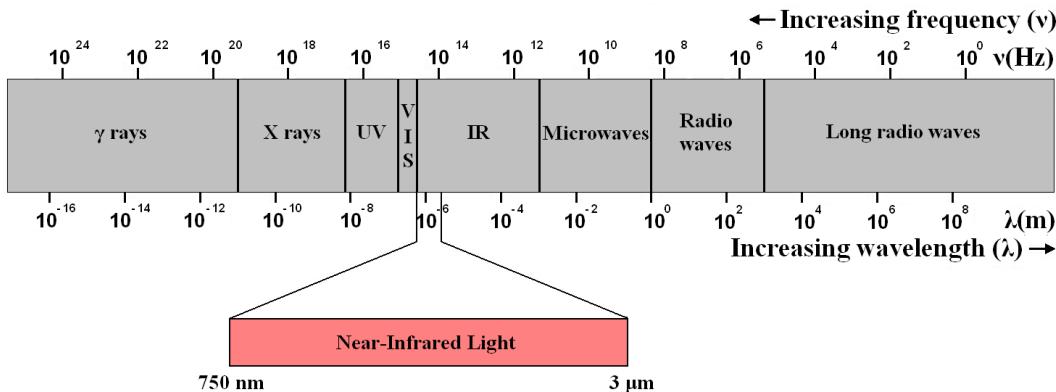
ML observed in two configurations:

- **Soft aperture** near stability limit
- With **hard aperture** within stability limits

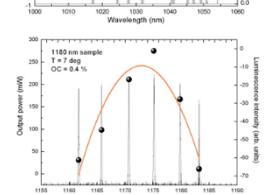
Kornaszewski et al, *Laser Photonics Rev.*, 6(6), L20, 2012

Gaafar et al, *Opt. Lett.*, v.39(15), p. 4623-4626, 2014

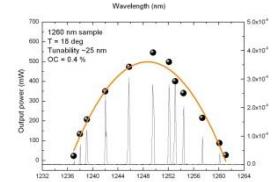
Compact QD-VECSEL sources



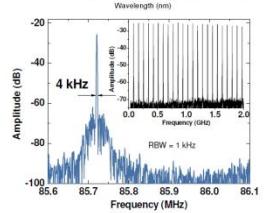
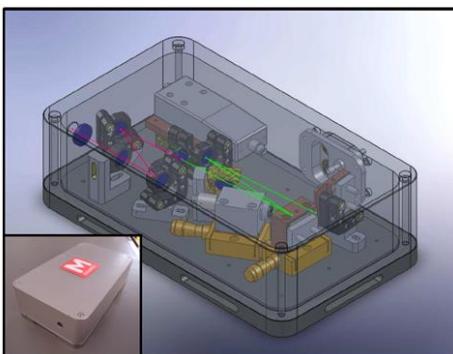
$D/\Delta \sim 60 \text{ nm at } 1030\text{nm}$
Up to 6 W in CW at 1040 nm
Up to 2 W in CW at 514 nm



$D/\Delta \sim 69 \text{ nm at } 1180\text{nm}$
Up to 6 W in CW at 1180 nm
Up to 2.5 W in CW at 590nm



$D/\Delta \sim 25 \text{ nm at } 1260\text{nm}$
Up to 1.6 W in CW at 1270 nm
Up to 0.33 W in CW at 624nm



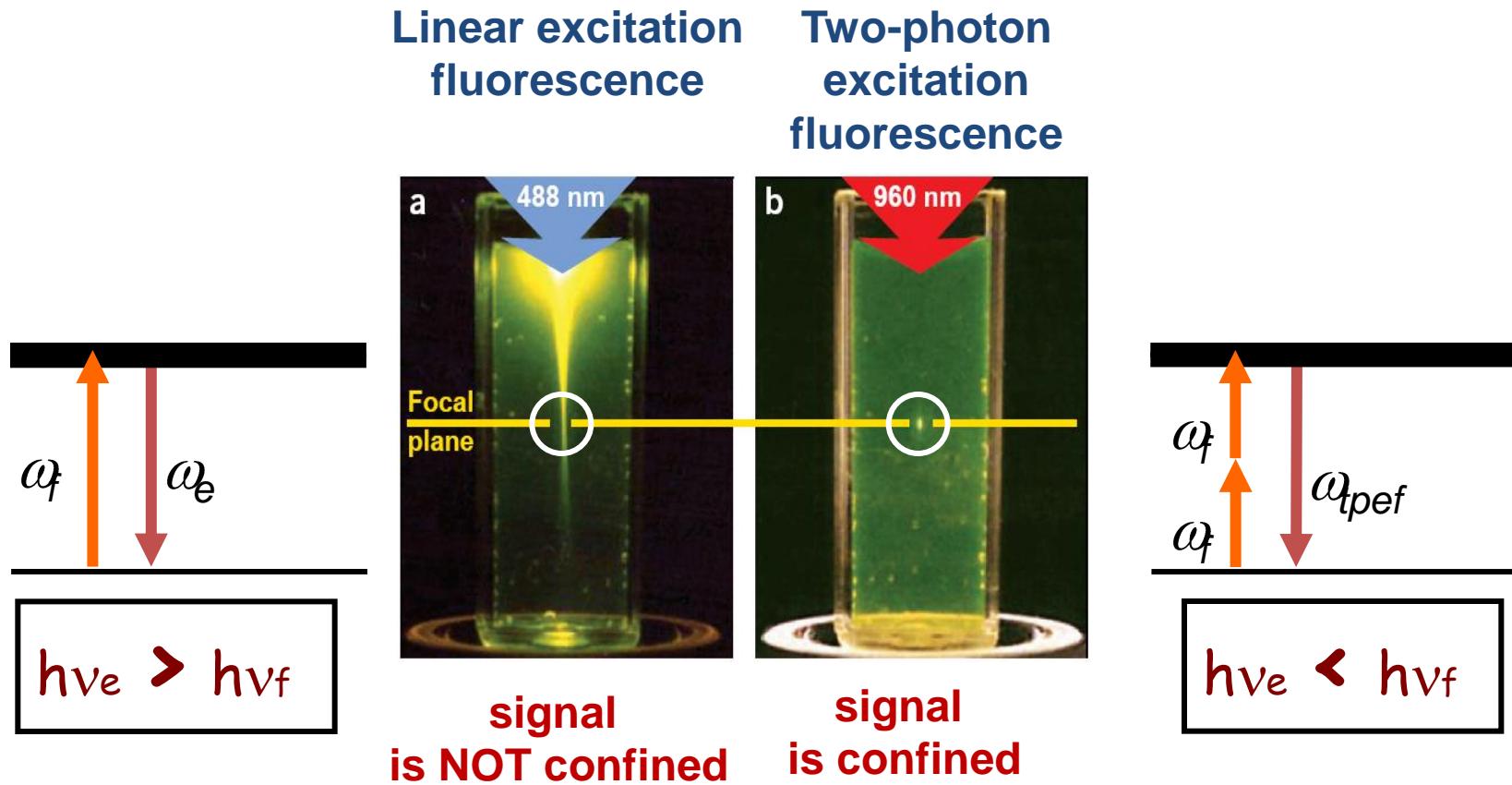
Up to 1 W in pulsed regime
Short pulse duration 870 fs
Ultra low repetition rate 85.7 MHz

Applications

- Fluorescence microscopy
- Spectroscopy
- Optical coherence tomography
- Cell-surgery
- Dermatology (e.g. photodynamic therapy of cancer)
- Cosmetic treatments (tattoo removal, hair removal)
- Ophthalmology
- Dentistry
- Blood analysis
- Frequency-conversion



Multi-photon Imaging



Single Photon Excitation: Lots of absorption everywhere, sample damage and no intrinsic sectioning

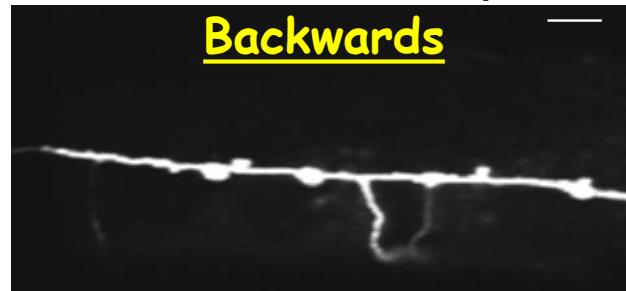
Multi-Photon Excitation: Absorption/excitation only in focal volume, less damage, live sample imaging, 3-D scanning, longer wavelength=less scatter



Multi-photon imaging with femtosecond laser

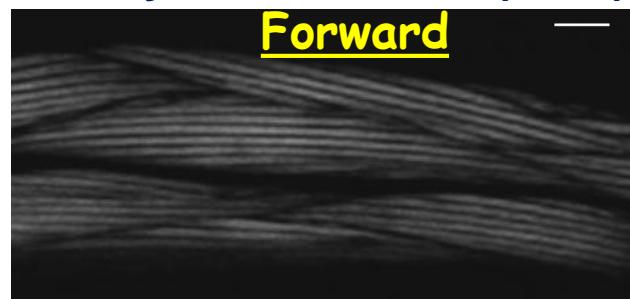
GFP labelled neurons (two-photon excited fluorescence - TPEF)

Backwards



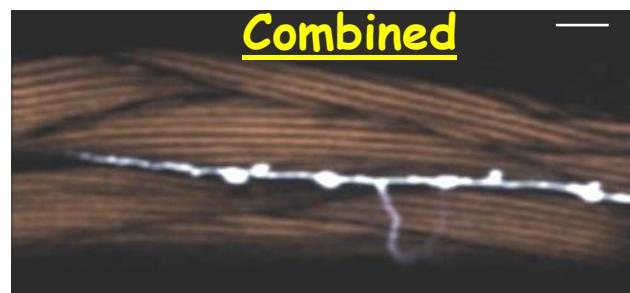
Body wall muscles (SHG)

Forward

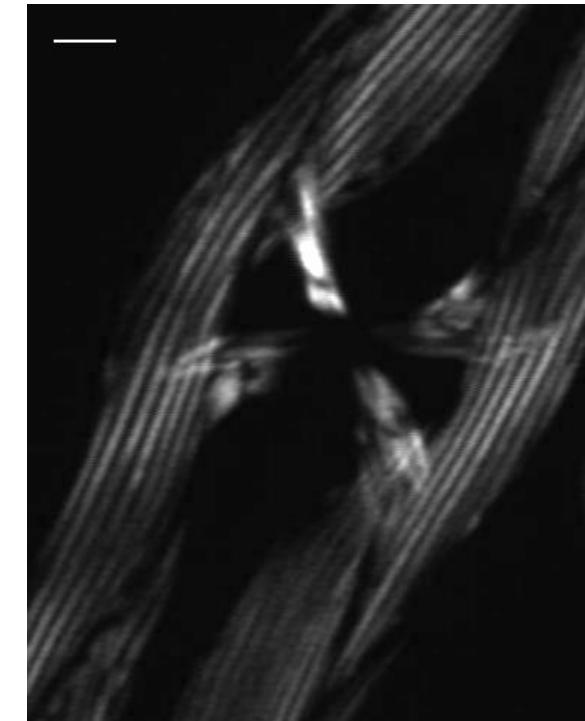


C. Elegans

Combined



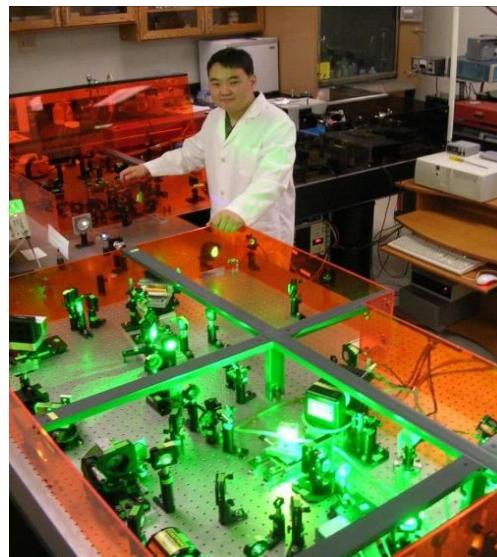
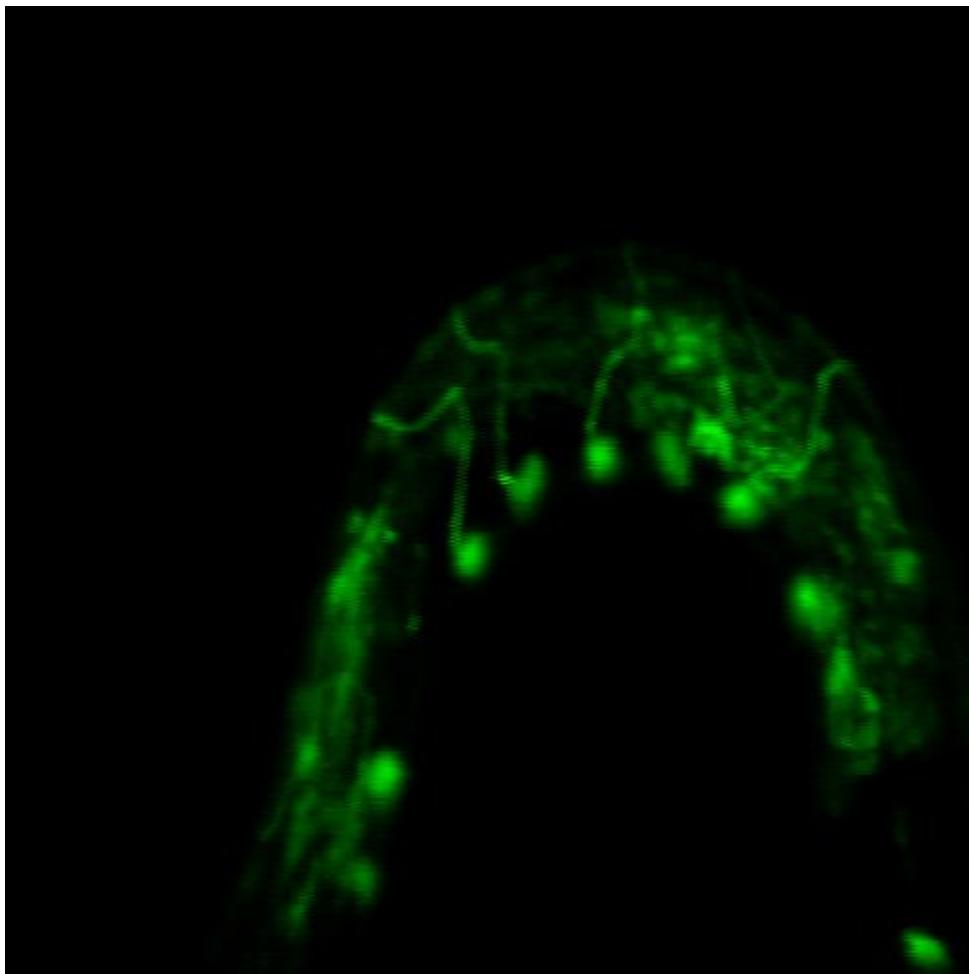
SHG Imaging of Vulva Muscles and body walls



ICFO Barcelona

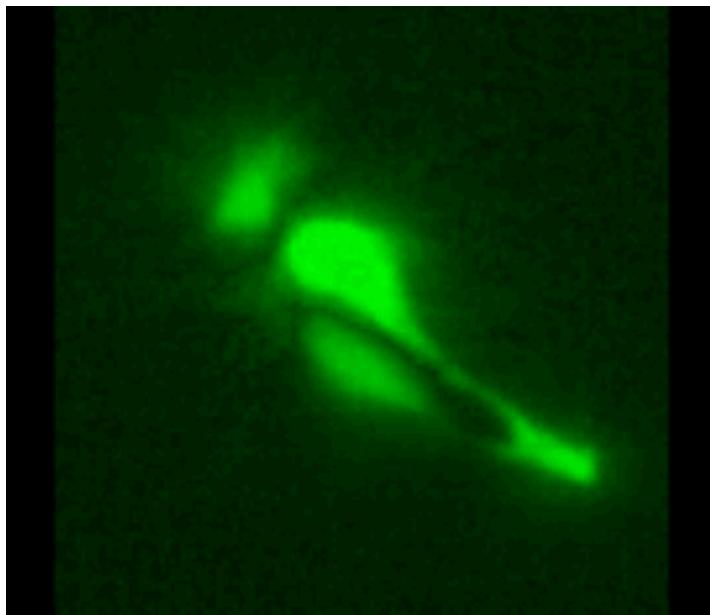


Multi-photon imaging with femtosecond laser

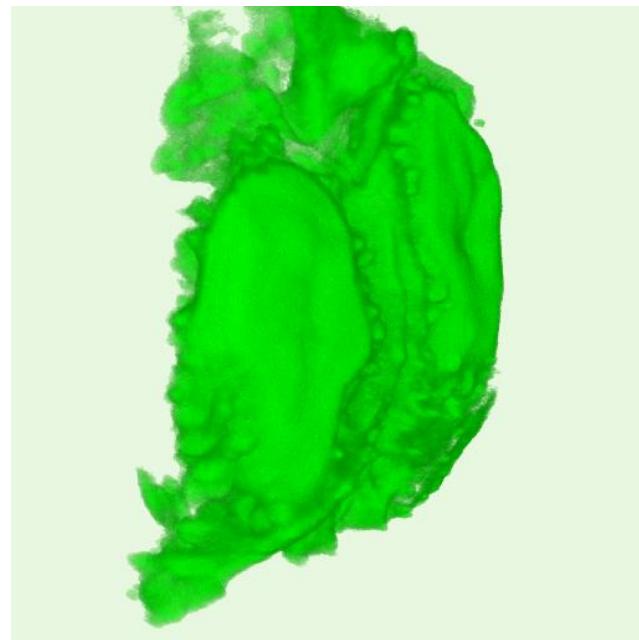


Green fluorescent protein (GFP) labeled Neurons in *C.elegans* using two-photon excited fluorescence (TPEF) microscopy

Multi-photon imaging with compact laser



3D stacks of living C.elegans. Shown here are the 3D-projections of a nerve ring stained with green fluorescent protein (GFP)



3D stacks of mice liver

Courtesy of MMI GmbH

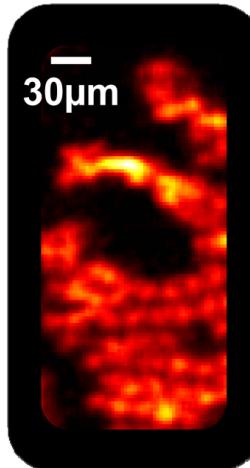


TPEF imaging from the MOPA system

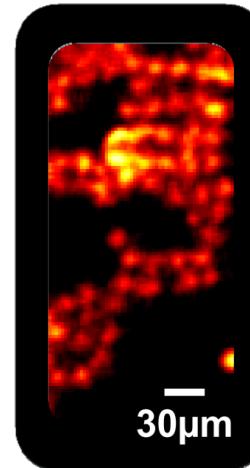
Microscopy setup and TPEF acquisition parameters:

Laser	Objective	Pulse width	Avg. Pow. at the S. plane	Peak Pow. at the S. Plane
	NA	[ps]	[mW]	[W]
SLD + SOA ext Cavity	1.4	~ 9	~ 18-23	~ 3-4

Nonlinear Microscope



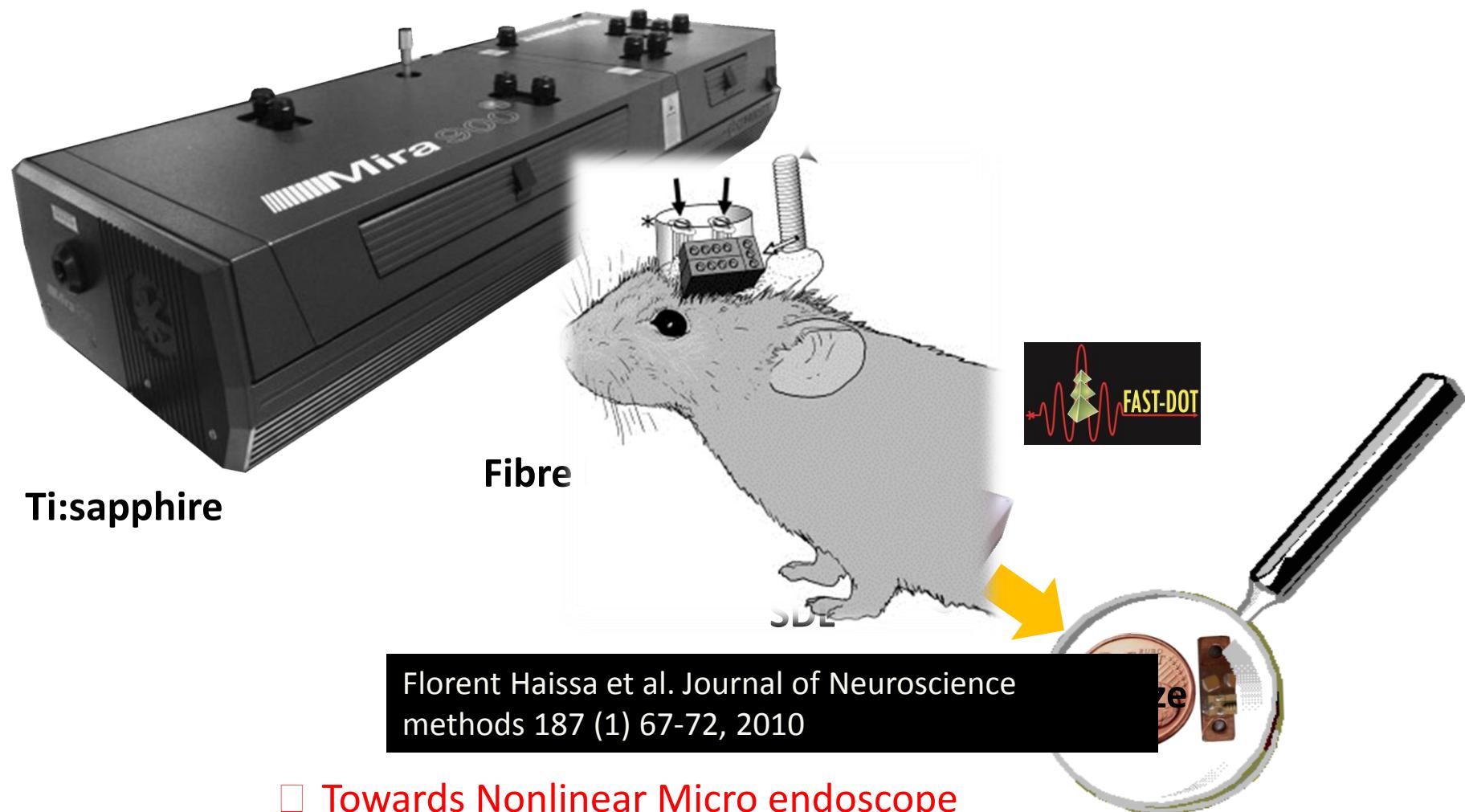
30μm



30μm

TPEF image of 15μm Crimson fluorescent beads for blood flow determination imaged using the chip-sized based ultra-short pulsed laser system. The resulting images were obtained by averaging 10 frames to improve the signal-to-noise ratio.

Future perspectives



Conclusions

- The quantum-dot structures demonstrate big potential in ultrafast physics:
 - Broad band tunability
 - Generation of pico- and femtosecond pulses directly from edge-emitting laser diodes
 - Generation of pico- and femtosecond pulses directly from surface-emitting laser diodes
 - High-power
 - Efficient SHG
- The high potential applicability of QD-based lasers in Biophotonics

Acknowledgments

Optoelectronics and Biomedical Photonics Group

1. Dr. S. Sokolovski
2. Dr. N. Bazieva
3. Dr. A. Gorodetsky
4. Dr. K. Fedorova
5. Dr. Ilya Titkov
6. Dr. Yury Loika
7. Mr. Modestas Zulonas
8. Mr. Amit Yadav
9. New 6 MC Fellows

Our collaborators

